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**Sonoda et al.**

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(54) **SUBSTRATE TO WHICH FILM IS FORMED  
AND ORGANIC EL DISPLAY DEVICE**

USPC ..... 257/40, 88, 15, 28, E51.001; 438/64,  
438/73, 84

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See application file for complete search history.

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U.S.C. 154(b) by 0 days.

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(2), (4) Date: **Jul. 15, 2013**

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PCT Pub. Date: **Jul. 26, 2012**

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**C23C 14/04** (2006.01)  
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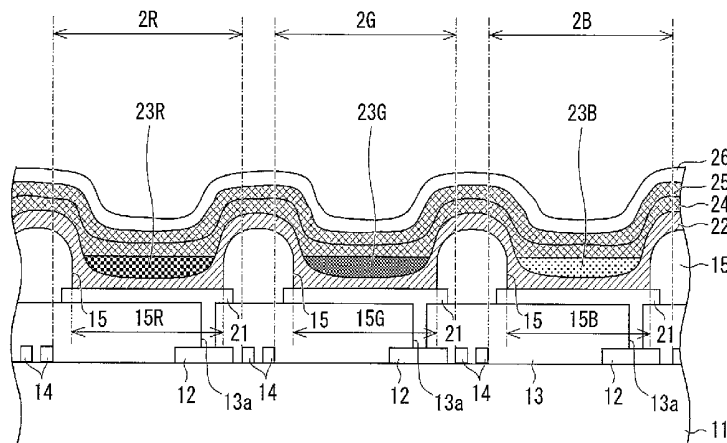
(57) **ABSTRACT**

On the TFT substrate (10), a vapor deposition layer is formed by use of a vapor deposition device (50) which includes (i) a vapor deposition source (85) having injection holes (86) and (ii) a vapor deposition mask (81) having openings (82) through which vapor deposition particles injected from the injection holes (86) are deposited so as to form the vapor deposition layer. The TFT substrate (10) has a plurality of pixels two-dimensionally arranged in a pixel region ( $A_G$ ), and terminals of a plurality of wires (14), which are electrically connected with the plurality of pixels, are gathered outside a vapor deposition layer formation region.

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H01M 14/00

**12 Claims, 15 Drawing Sheets**



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|------|--------------------------------------------------------------------------------------------------------------|---------------------|--------------------------|---------|--|--|
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|      | <i>14/24</i> (2013.01)                                                                                       |                     |                          |         |  |  |
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FIG. 1

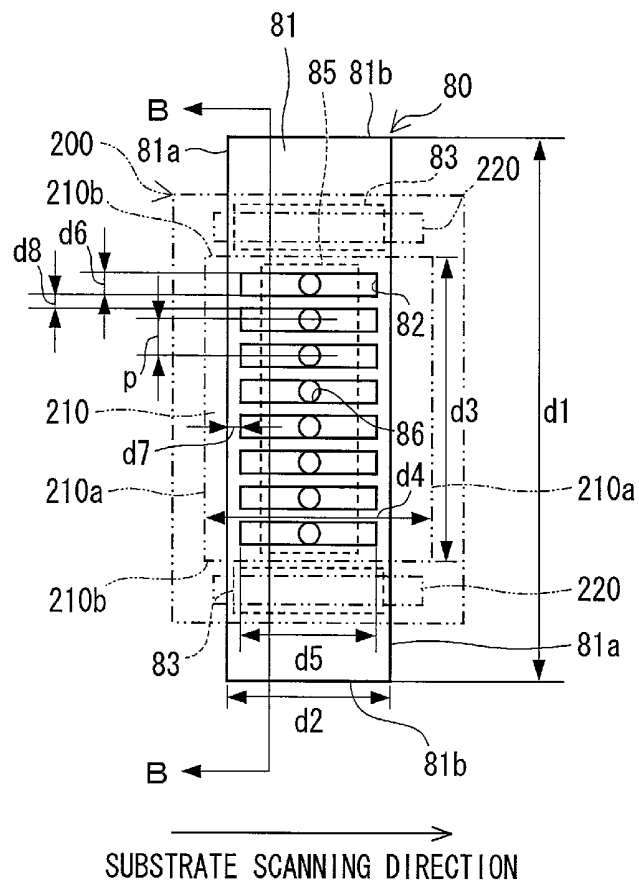


FIG. 2

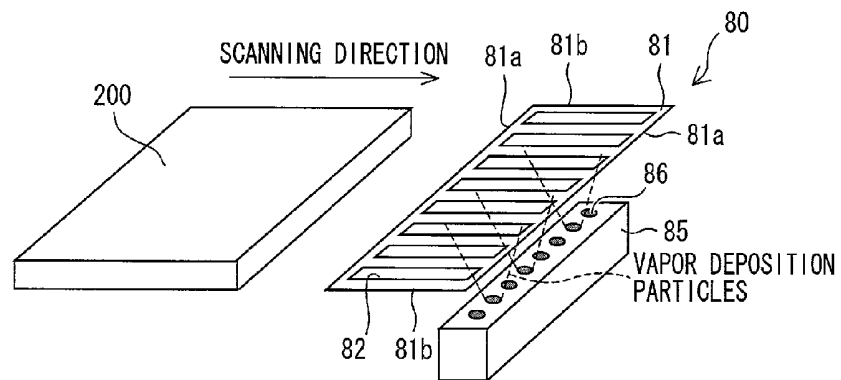


FIG. 3

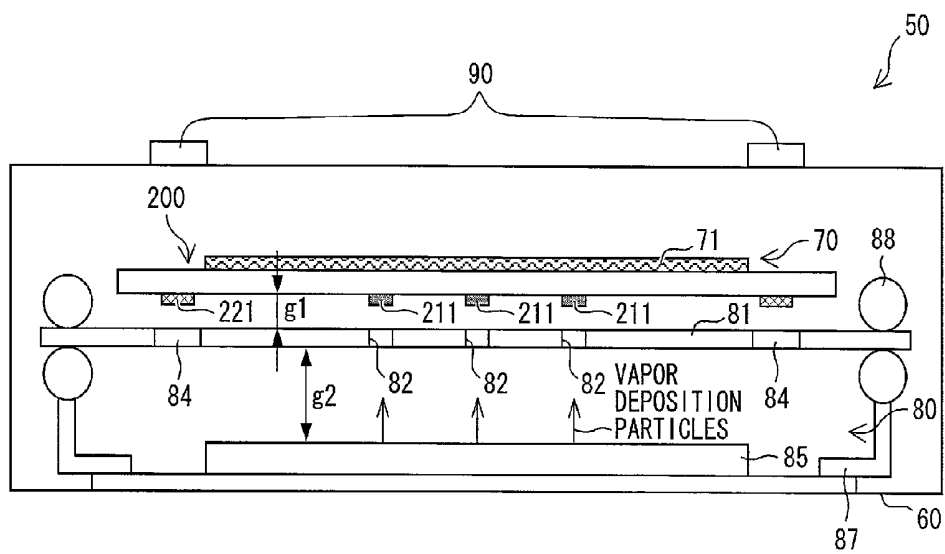


FIG. 4

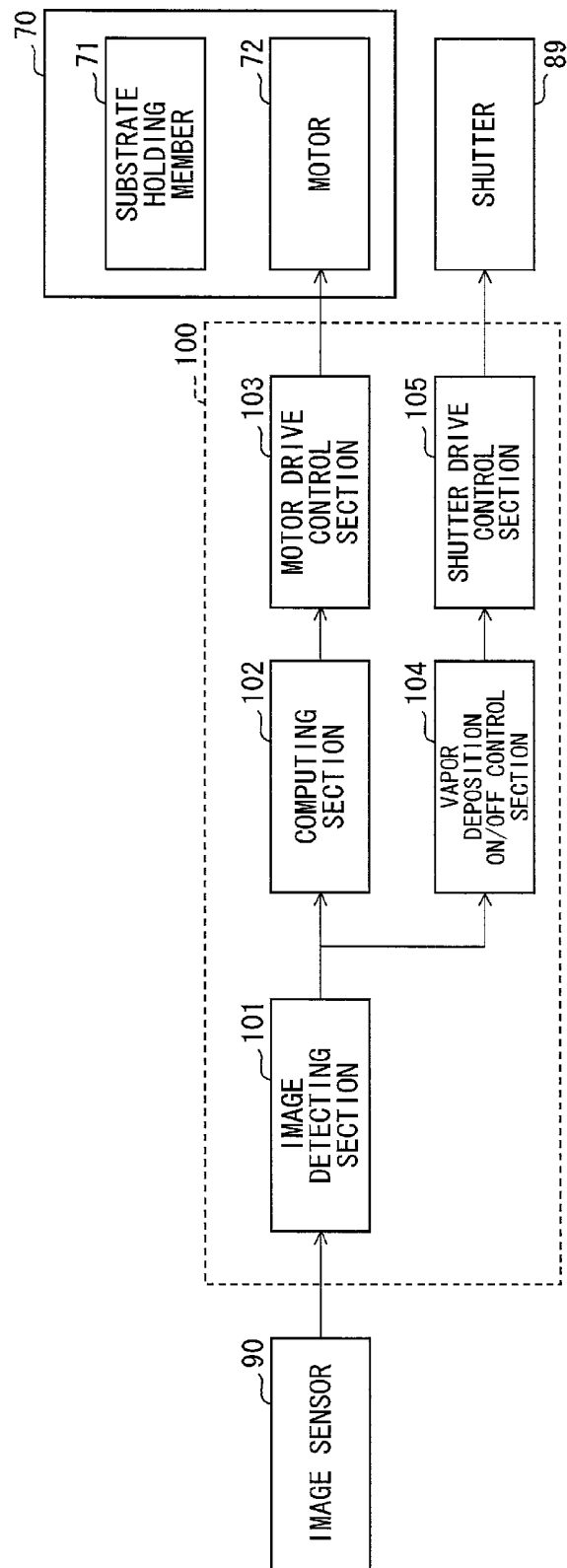


FIG. 5

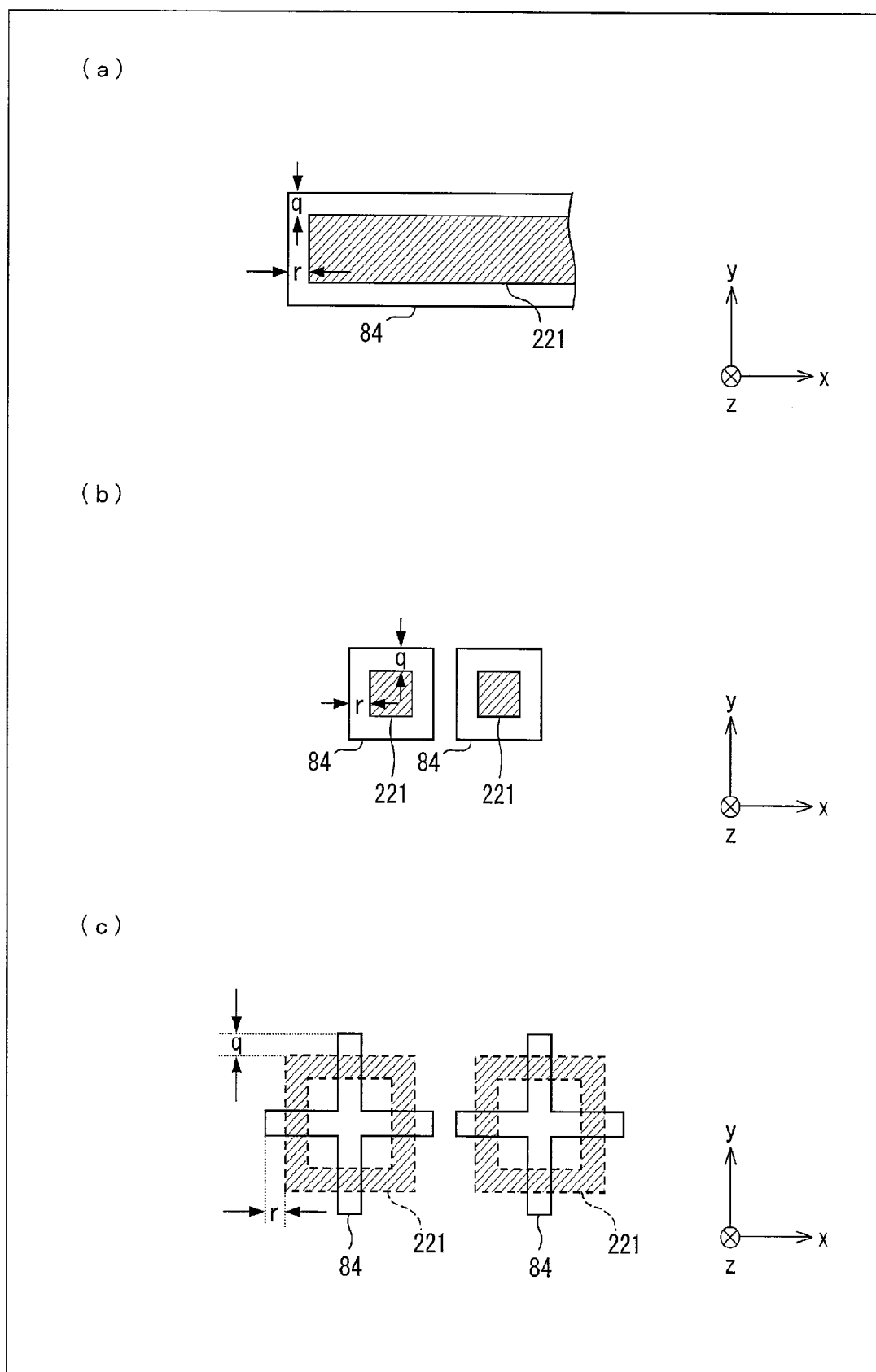


FIG. 6

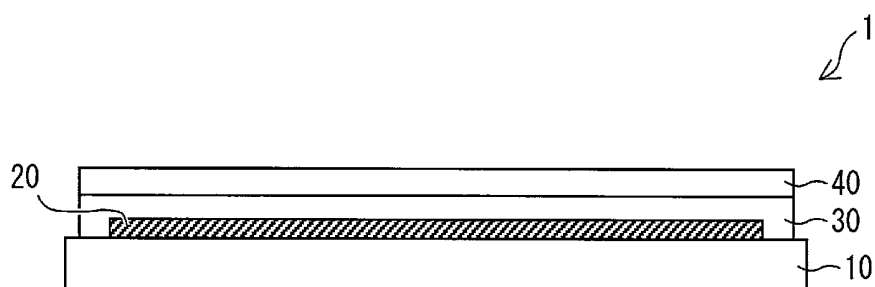
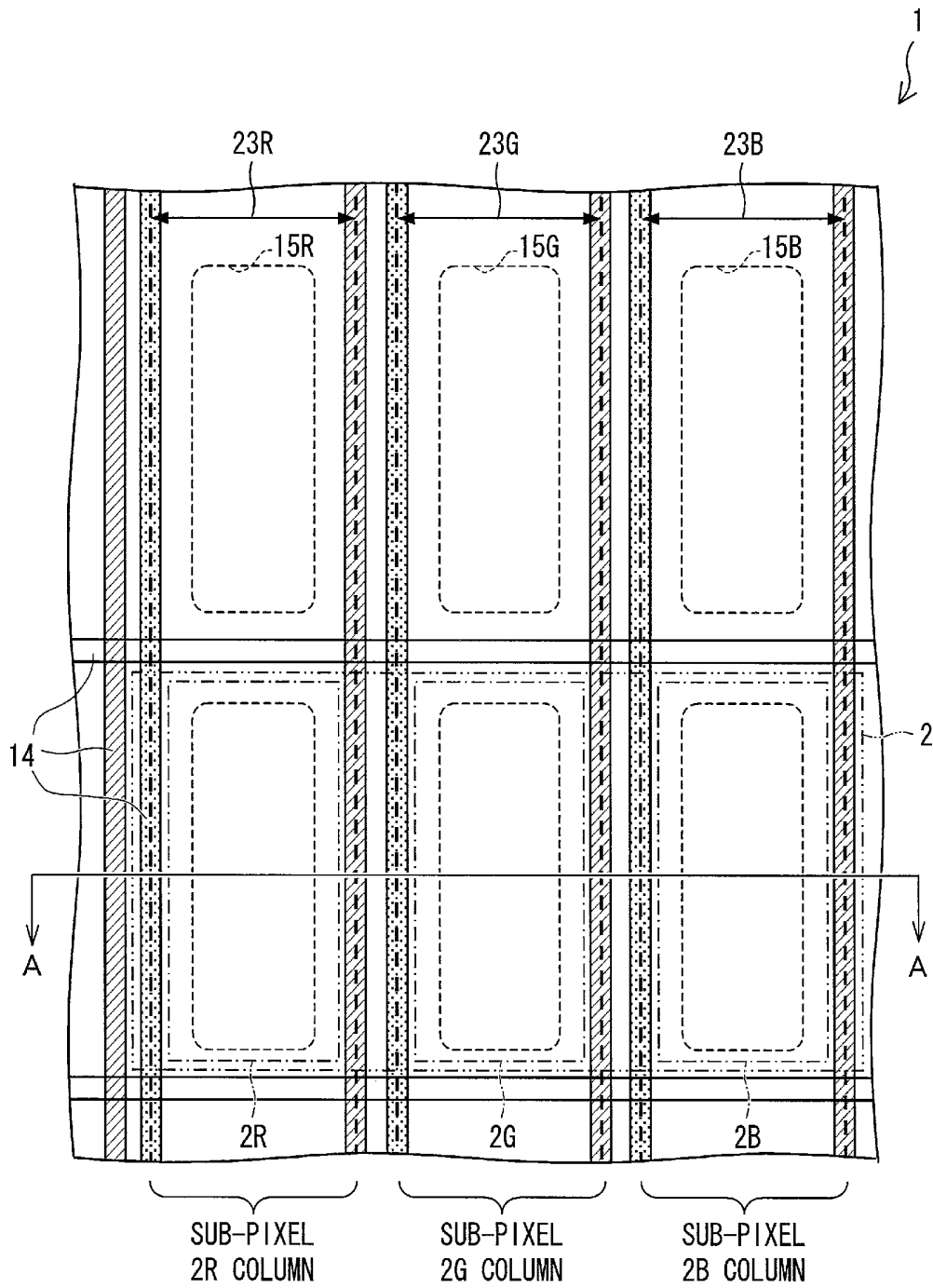


FIG. 7



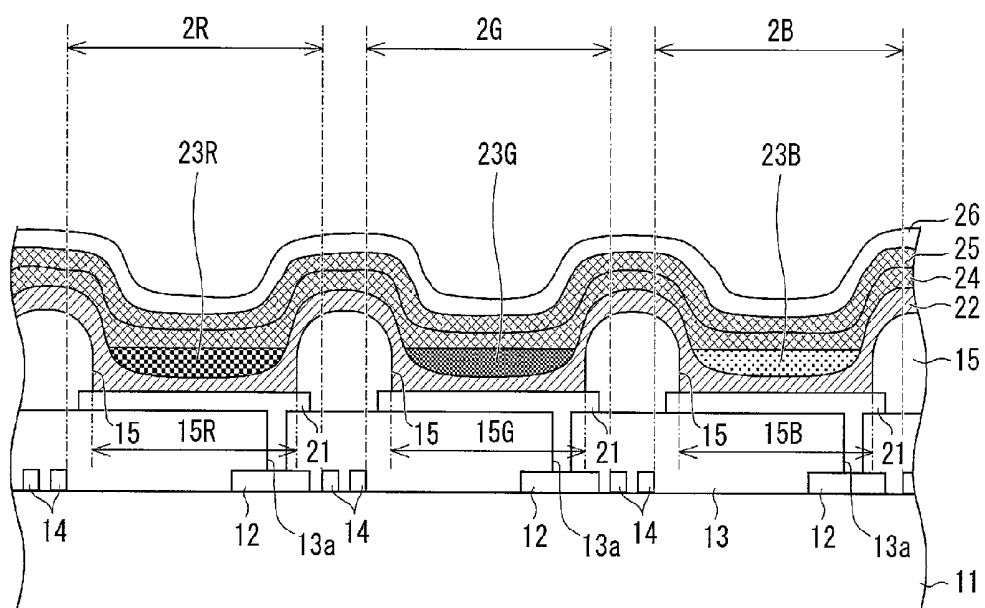


FIG. 9

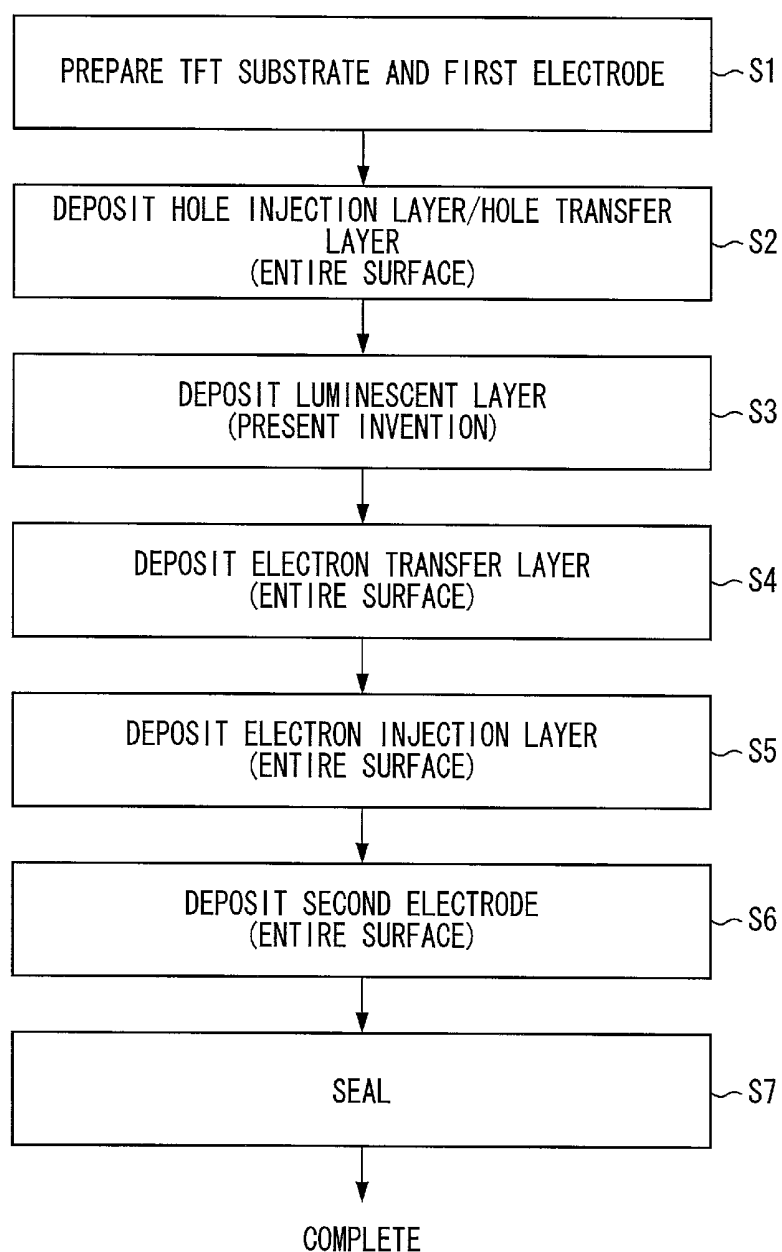


FIG. 10

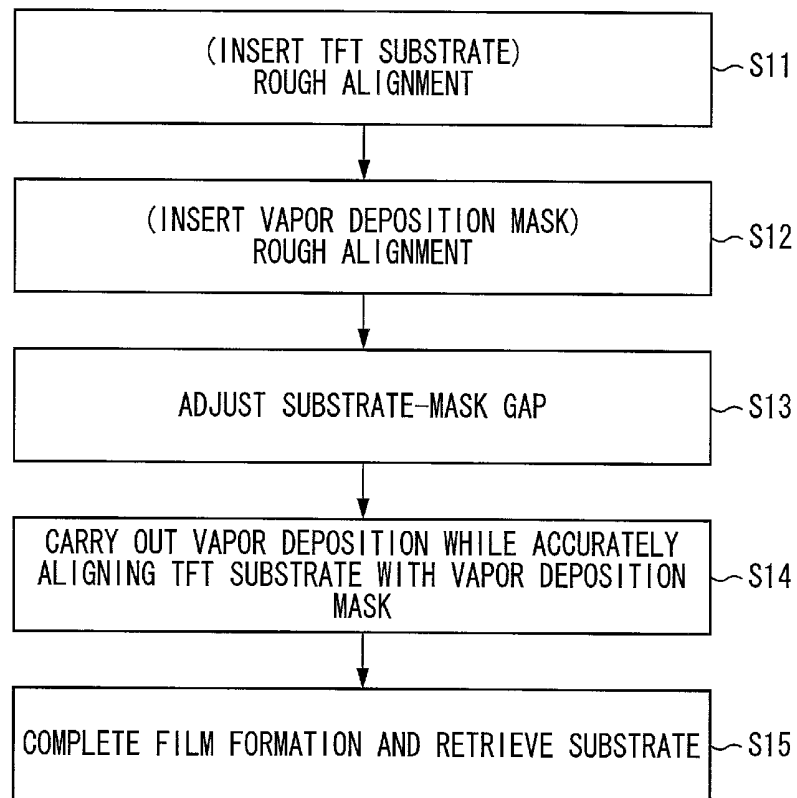


FIG. 11

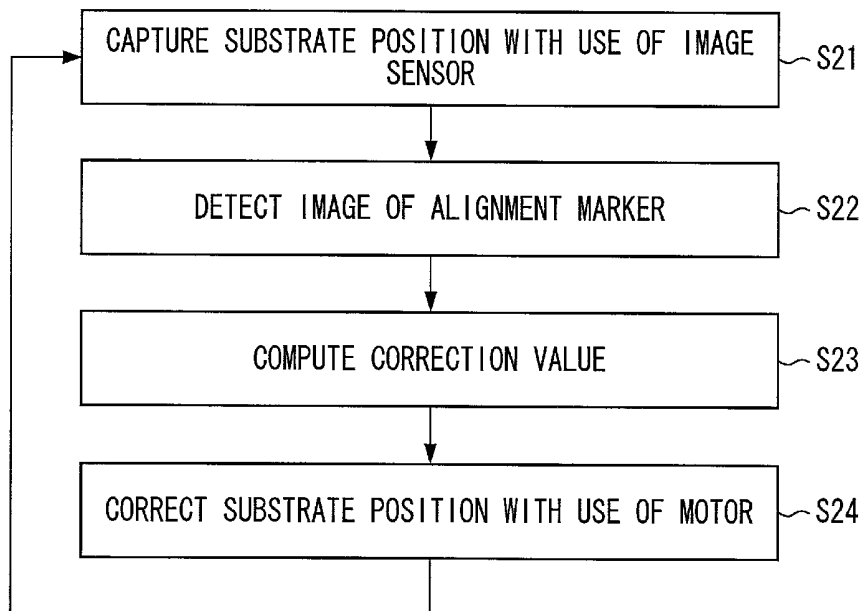


FIG. 12

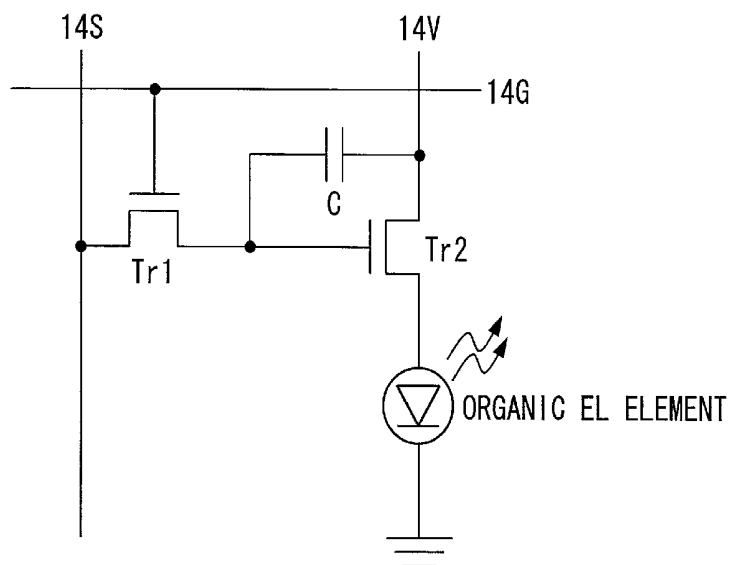


FIG. 13

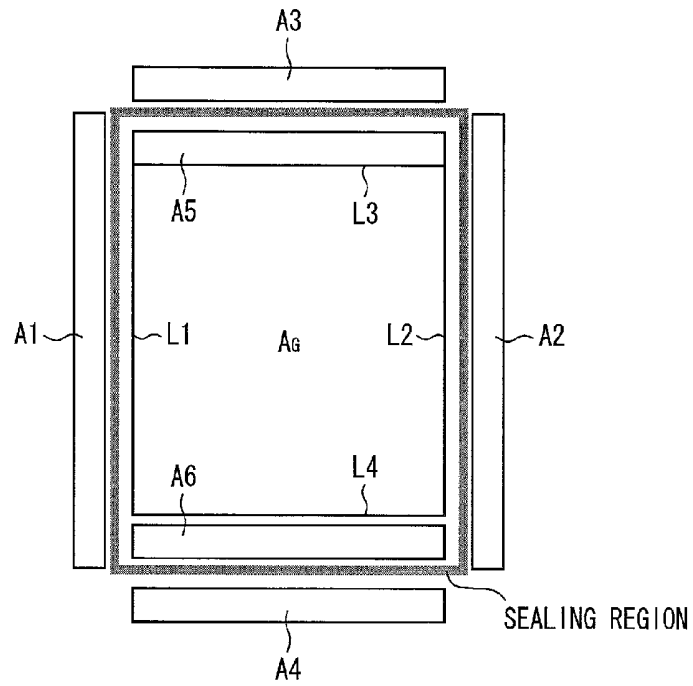


FIG. 14

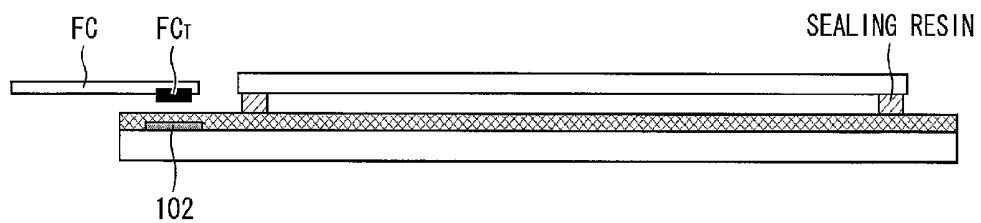


FIG. 15

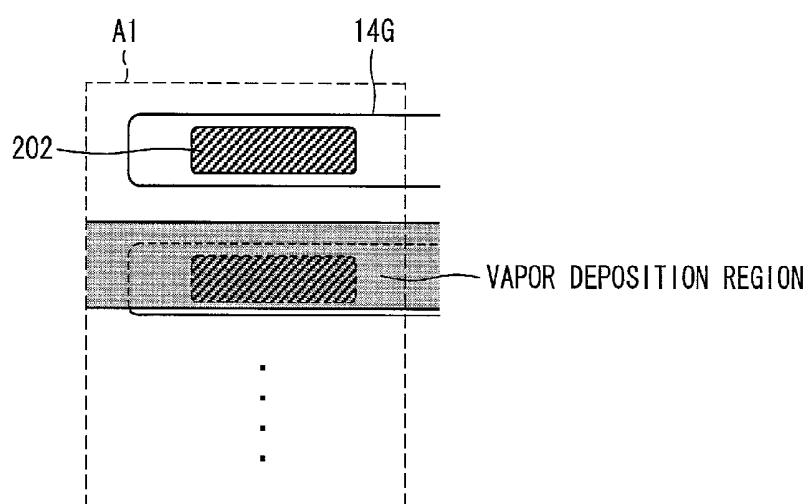


FIG. 16

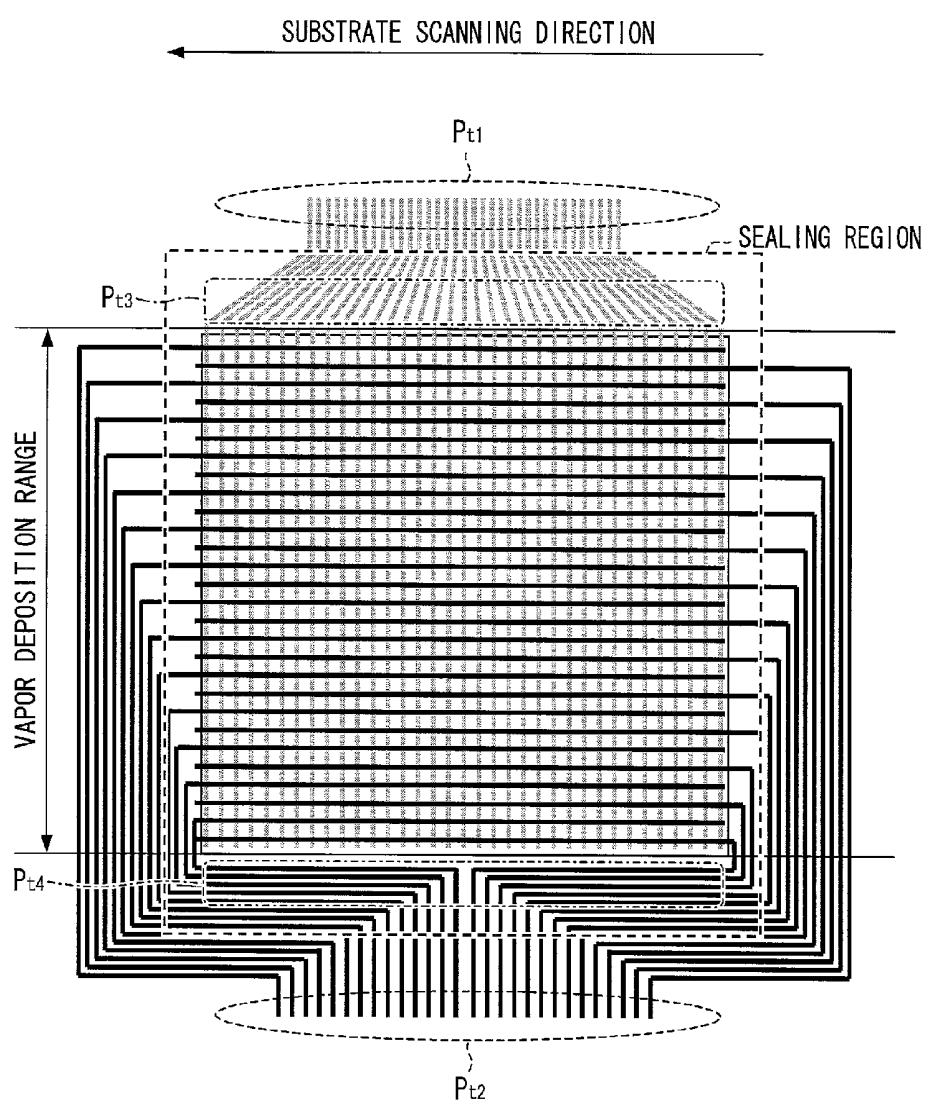


FIG. 17

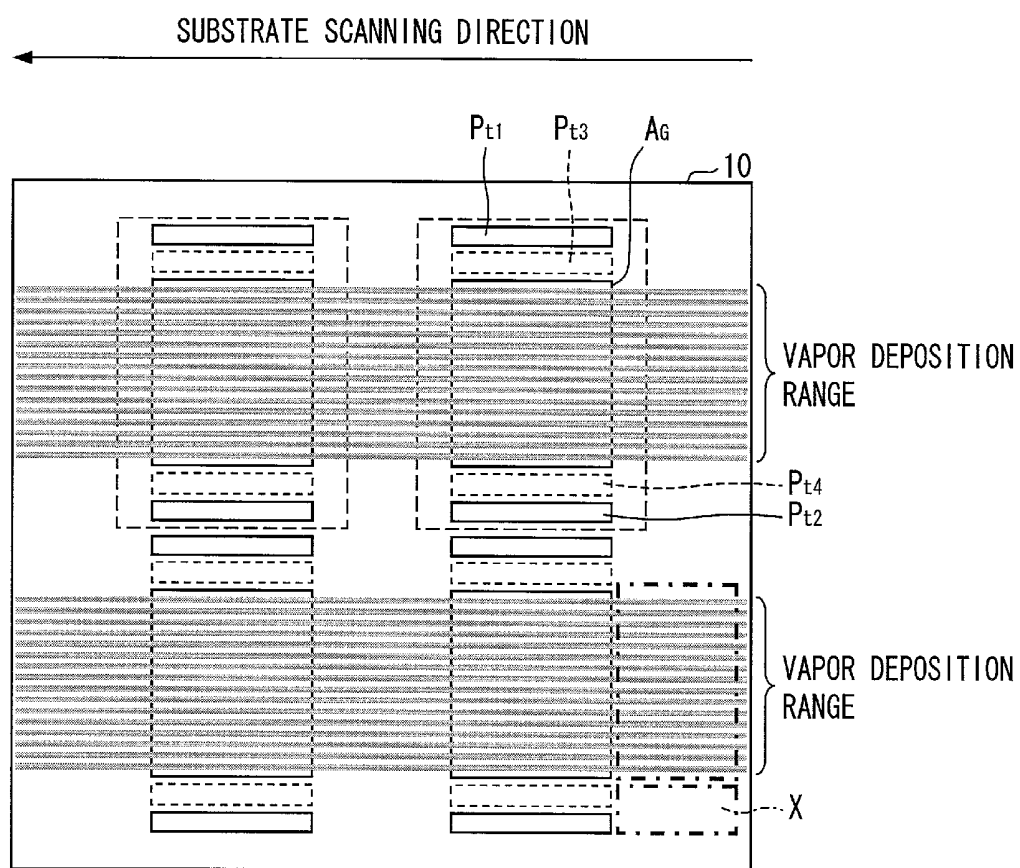


FIG. 18

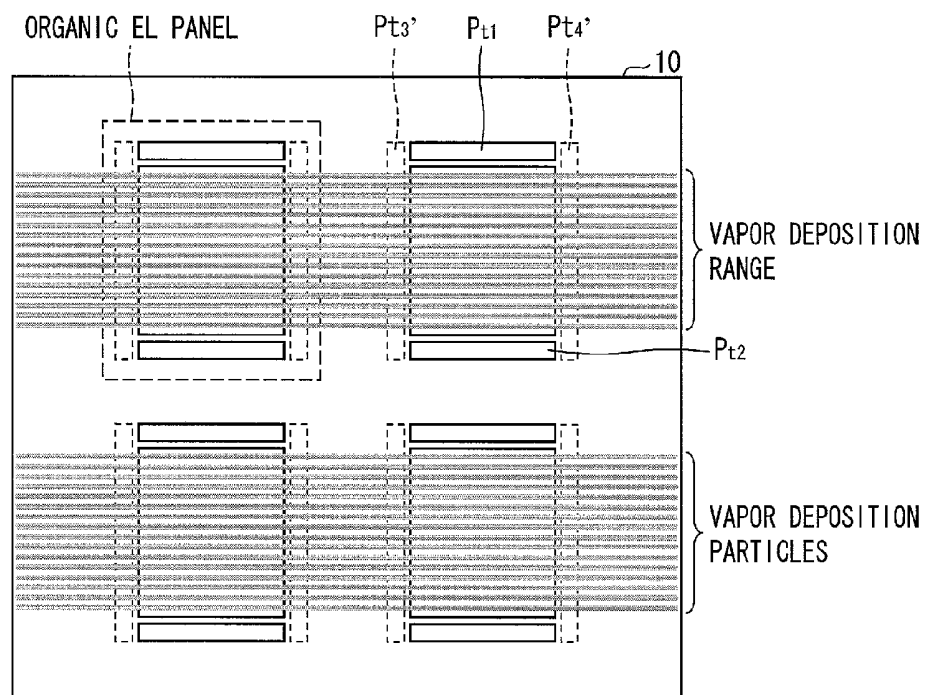
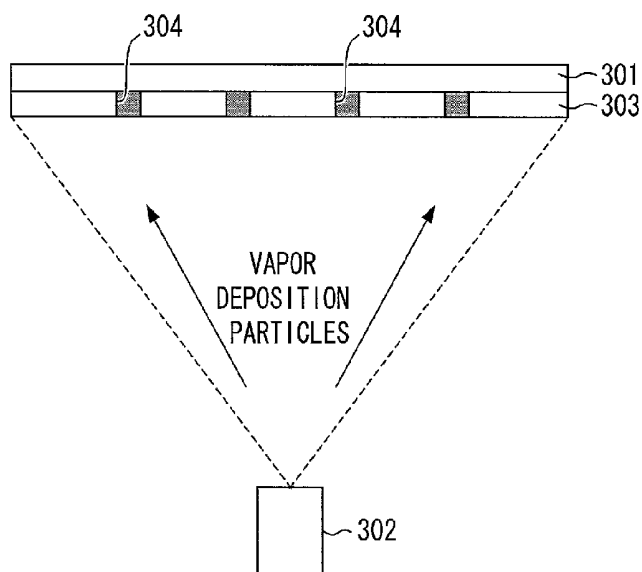


FIG. 19



# SUBSTRATE TO WHICH FILM IS FORMED AND ORGANIC EL DISPLAY DEVICE

## CROSS REFERENCE TO RELATED APPLICATIONS

This is a U.S. National Phase patent application of PCT/JP2012/050526, filed Jan. 12, 2012, which claims priority to Japanese Patent Application No. 2011-008106, filed Jan. 18, 2011, each of which is hereby incorporated by reference in the present disclosure in its entirety.

## TECHNICAL FIELD

The present invention relates to a technique of vapor deposition for forming a film of a predetermined pattern on a film formation substrate.

## BACKGROUND ART

Recent years have witnessed practical use of a flat-panel display in various products and fields. This has led to a demand for a flat-panel display that is larger in size, achieves higher image quality, and consumes less power.

Under such circumstances, great attention has been drawn to an organic EL display device that (i) includes an organic electroluminescence (hereinafter abbreviated to "EL") element which uses EL of an organic material and that (ii) is an all-solid-state flat-panel display which is excellent in, for example, low-voltage driving, high-speed response, and self-emitting.

An organic EL display device includes, for example, (i) a substrate made up of members such as a glass substrate and TFTs (thin film transistors) provided to the glass substrate and (ii) organic EL elements provided on the substrate and connected to the TFTs.

An organic EL element is a light-emitting element capable of high-luminance light emission based on low-voltage direct-current driving, and includes in its structure a first electrode, an organic EL layer, and a second electrode stacked on top of one another in that order, the first electrode being connected to a TFT. The organic EL layer between the first electrode and the second electrode is an organic layer including a stack of layers such as a hole injection layer, a hole transfer layer, an electron blocking layer, a luminescent layer, a hole blocking layer, an electron transfer layer, and an electron injection layer.

A full-color organic EL display device typically includes organic EL elements of red (R), green (G), and blue (B) as sub-pixels aligned on a substrate. The full-color organic EL display device carries out an image display by, with use of TFTs, selectively causing the organic EL elements to each emit light with a desired luminance.

Such an organic EL display device is produced through a process that forms, for each organic EL element serving as a light-emitting element, a pattern of a luminescent layer made of an organic luminescent material which emits light of at least the above three colors (see, for example, Patent Literatures 1 and 2).

Such formation of a luminescent layer pattern is performed by a method such as a vacuum vapor deposition method that uses a vapor deposition mask referred to as a shadow mask.

The production of, for example, a low-molecular organic EL display (OLED) has conventionally used a vapor deposition method involving a shadow mask, the vapor deposition method forming organic films (organic layers) by selective application.

The vacuum vapor deposition method involving a shadow mask uses a shadow mask (full-cover contact type shadow mask) that is so sized as to allow vapor deposition to be performed throughout the entire vapor deposition region of a substrate. The shadow mask is typically equivalent in size to the substrate.

FIG. 19 is a cross-sectional view schematically illustrating a configuration of a conventional vapor deposition device involving a shadow mask.

The vacuum vapor deposition method involving a shadow mask, as illustrated in FIG. 19, forms a pattern by (i) placing a substrate 301 and a vapor deposition source 302 at such positions that the substrate 301 and the vapor deposition source 302 face each other, (ii) forming, in a shadow mask 303, openings 304 corresponding to a pattern of a portion of a target vapor deposition region so that no vapor deposition particles are adhered to a region other than the vapor deposition region, and (iii) depositing vapor deposition particles onto the substrate 301 through the openings 304.

The substrate 301 is placed in a vacuum chamber (not shown). The vapor deposition source 302 is fixed below the substrate 301. The shadow mask 303 is either fixed in close contact with the substrate 301 or moved relative to the substrate 301 while the substrate 301 and the vapor deposition source 302 are fixed to an inner wall of the vacuum chamber.

Patent Literature 1, for example, discloses a method that involves a load-lock vapor deposition source, the method (i) aligning a mask and a substrate with each other, next (ii) performing vacuum vapor deposition of a first luminescent material from directly below the substrate to form an arrangement of first light-emitting sections each substantially identical in shape to an opening of the mask, then (iii) shifting the mask, and (iv) performing vacuum vapor deposition of a second luminescent material from directly below the substrate to form an arrangement of second light-emitting sections each substantially identical in shape to the opening of the mask.

Patent Literature 2, for example, discloses a method for forming an electrode pattern, the method (i) aligning, in a mask equivalent in size to a substrate, short-diameter holes or long and narrow slit pores in a direction which intersects a direction in which the mask is shifted and (ii) performing vapor deposition of an electrode material while the mask is shifted in a direction in which the short-diameter holes or slit pores are aligned.

In the vacuum vapor deposition method involving a shadow mask as described above, the shadow mask is fixed (for example, welded) to a mask frame under tension for prevention of, for example, bending and distortion.

The vacuum vapor deposition method involving a shadow mask forms a luminescent layer pattern or an electrode pattern by (i) closely contacting a shadow mask such as the above with a substrate and (ii) causing vapor deposition particles from a vapor deposition source to be deposited (adhered) onto a desired position of the substrate through an opening of the shadow mask.

## CITATION LIST

### Patent Literature 1

Japanese Patent Application Publication, Tokukai, No. 2000-188179 A (Publication Date: Jul. 4, 2000) (corresponding U.S. Pat. No. 6,294,892 (Publication Date: Sep. 25, 2001))

Patent Literature 2

Japanese Patent Application Publication, Tokukaihei, No. 10-102237 A (Publication Date: Apr. 21, 1998)

## SUMMARY OF INVENTION

### Technical Problem

Unfortunately, a larger substrate size requires the shadow mask 303 to be larger in size as well.

Such a larger size results in a gap opening between the substrate 301 and the shadow mask 303 due to, for example, self-weight bending and elongation of the shadow mask 303. This makes it impossible to form a pattern with high positional accuracy, and thus causes, for example, misplacement in vapor deposition and color mixture, thereby making it difficult to achieve high resolution.

Further, a larger substrate size requires the shadow mask 303 and a mask frame that holds it to be both extremely large and heavy. This in turn requires a device that uses the shadow mask 303 to be extremely large and complex, which not only makes it difficult to design such a device, but also causes a safety problem in handling the shadow mask during a production step or a step such as replacing the shadow mask.

It is, in consequence, extremely difficult to form a pattern on a large-sized substrate with use of a large-sized shadow mask.

A process of producing an organic EL display device requires a substrate size of approximately 1 m per side in order to use an existing mass production process of the vapor deposition method involving a full-cover contact type shadow mask. It is difficult to use the vapor deposition method for a large-sized substrate having a substrate size larger than approximately 1 m per side. This indicates that there currently exists no established organic layer selective application technique that is usable for a large-sized substrate. It is thus impossible to mass-produce a large-sized organic EL display device of a 60-inch class or a larger size.

A larger substrate size normally allows a larger number of panels to be formed from a single substrate, and thus reduces the unit cost of a panel. This means that a larger sized substrate allows an organic EL display device to be produced at a lower cost. Conventionally, however, the above constraint in substrate size has prevented production of a low-cost organic EL display device.

One solution to these problems is to reduce an area of the shadow mask 303 by employing an arrangement in which vapor deposition is carried out by moving at least one of the substrate and the shadow mask 303 relative to the other in a direction while securing a predetermined gap between the substrate and the shadow mask 303.

However, such an arrangement causes the following problem.

Specifically, the substrate generally has a region on which vapor deposition particles need not to be vapor-deposited or a region on which vapor deposition particles should not be vapor-deposited (these regions are hereinafter referred to as "vapor deposition unnecessary region"). The vapor deposition unnecessary region is, for example, a connection section (terminal section) in which terminals for connection with an external circuit are gathered. No vapor deposition is carried out on the terminals, and thus the terminals are exposed.

The arrangement, in which the substrate is moved relative to the shadow mask so that vapor deposition is carried out throughout a region from one end to the other end in a direction in which the substrate is moved, cannot establish good electrical connection between the connection section (termi-

nal section) and the external circuit in a case where (i) a region on which the vapor deposition is carried out includes the vapor deposition unnecessary region and (ii) an organic film that has high electrical resistance is formed by the vapor deposition.

One solution to this problem is to employ an arrangement in which vapor deposition is blocked by use of a shutter so that vapor deposition is not carried out in the vapor deposition unnecessary region.

However, such an arrangement leaves, depending on, for example, a shape of openings of a shadow mask, a region in which vapor deposition has not been carried out or a region in which vapor deposition has not been fully completed when the vapor deposition is blocked. This results in a problem that the organic film cannot have an appropriate thickness in such a region.

Another solution is to wipe away the organic film with the use of an organic solvent in a later step. However, such a method undesirably generates a residue of the organic solvent and introduces dust, and, as a consequence, decreases reliability of a product. In addition, such a method necessitates another step of wiping away the organic film. This means an increase in the number of steps, inviting an increase in time and cost for production.

The present invention was accomplished in view of the above problems, and an object of the present invention is to provide a film formation substrate and an organic EL device each of which makes it possible to prevent vapor deposition in a vapor deposition unnecessary region while preventing or suppressing a decline in reliability of a product.

### Solution to Problem

In order to attain the object, a film formation substrate of the present invention is a film formation substrate on which a vapor deposition layer is formed by use of a vapor deposition device which includes (i) a vapor deposition source having an injection hole from which vapor deposition particles are injected and (ii) a vapor deposition mask facing the vapor deposition source and having an opening through which the vapor deposition particles injected from the injection hole are deposited so as to form the vapor deposition layer, the film formation substrate including: a plurality of pixels two-dimensionally arranged in a pixel region; and a plurality of wires electrically connected to the respective plurality of pixels, the vapor deposition layer being formed in a vapor deposition layer formation region, which includes the pixel region, by injecting the vapor deposition particles from the injection hole while moving the film formation substrate relative to the vapor deposition mask in a moving direction so that the pixel region passes a region facing the opening, and terminals of the plurality of wires being gathered outside the vapor deposition layer formation region.

According to the invention, vapor-deposited films are formed by moving the film formation substrate relative to the vapor deposition mask in a direction. This makes it possible to use a vapor deposition mask that is small in size. Use of such a small-size vapor deposition mask does not cause problems, such as self-weight bending and elongation, which arise from an increase in size of a vapor deposition mask. It is therefore possible to not only form a pattern of a vapor-deposited layer on a large-sized substrate, but also form such a pattern with high positional accuracy and high resolution.

Further, use of such a small-size vapor deposition mask makes it possible to suppress or prevent problems which occur in a case where an increase in size of a vapor deposition

mask causes a frame for holding the vapor deposition mask to be extremely large and extremely heavy.

In addition, the film formation substrate of the present invention has the pixel region in which the plurality of pixels which are two-dimensionally arranged, and the terminals of the plurality of wires, which are electrically connected with the respective plurality of pixels in the pixel region, are gathered outside the vapor deposition layer formation region.

Accordingly, even by injecting the vapor deposition particles from the injection holes while moving the film formation substrate relative to the vapor deposition mask in a direction, no vapor-deposited layer is formed in regions where the terminals of the plurality of wires are gathered. It is therefore possible to provide a film formation substrate which makes it possible to prevent vapor deposition in vapor deposition unnecessary regions while preventing or suppressing a decline in reliability of a product.

#### Advantageous Effects of Invention

As above described, the film formation substrate of the present invention is a film formation substrate on which a vapor deposition layer is formed by use of a vapor deposition device which includes (i) a vapor deposition source having an injection hole from which vapor deposition particles are injected and (ii) a vapor deposition mask facing the vapor deposition source and having an opening through which the vapor deposition particles injected from the injection hole are deposited so as to form the vapor deposition layer, the film formation substrate including: a plurality of pixels two-dimensionally arranged in a pixel region; and a plurality of wires electrically connected to the respective plurality of pixels, the vapor deposition layer being formed in a vapor deposition layer formation region, which includes the pixel region, by injecting the vapor deposition particles from the injection hole while moving the film formation substrate relative to the vapor deposition mask in a moving direction so that the pixel region passes a region facing the opening, and terminals of the plurality of wires being gathered outside the vapor deposition layer formation region.

The arrangement makes it possible to provide a film formation substrate which makes it possible to prevent vapor deposition in a vapor deposition unnecessary region while preventing or suppressing a decline in reliability of a product.

#### BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a plan view illustrating a film formation substrate and a mask unit inside a vacuum chamber of a vapor deposition device according to an embodiment of the present invention, the plan view being taken from a back surface side of the film formation substrate.

FIG. 2 is a bird's eye view illustrating main constituent elements inside the vacuum chamber of the vapor deposition device according to the embodiment of the present invention.

FIG. 3 is a cross-sectional view schematically illustrating a configuration of a main part of the vapor deposition device according to the embodiment of the present invention.

FIG. 4 is a block diagram partially illustrating a configuration of the vapor deposition device according to the embodiment of the present invention.

(a) through (c) of FIG. 5 are each a diagram illustrating example shapes of alignment markers provided to the film formation substrate and a vapor deposition mask according to the embodiment of the present invention.

FIG. 6 is a cross-sectional view schematically illustrating a configuration of an organic EL display device for carrying out an RGB full color display.

FIG. 7 is a plan view illustrating an arrangement of pixels constituting the organic EL display device illustrated in FIG. 6.

FIG. 8 is a cross-sectional view, taken along line A-A, illustrating a TFT substrate in the organic EL display device illustrated in FIG. 7.

FIG. 9 is a flowchart indicating successive steps for producing the organic EL display device according to the embodiment of the present invention.

FIG. 10 is a flowchart indicating an example method for forming a predetermined pattern on a TFT substrate with use of the vapor deposition device according to the embodiment of the present invention.

FIG. 11 is a flowchart indicating an alignment adjustment method.

FIG. 12 is a view illustrating a configuration of a TFT circuit.

FIG. 13 is a view schematically illustrating how a TFT substrate is configured before formation of luminescent layers.

FIG. 14 is a view illustrating a state where the TFT substrate 10 sealed by a sealing substrate is about to be connected to a flexible film cable.

FIG. 15 is a view illustrating a region around terminals of wires in a vertical-side terminal section region.

FIG. 16 is a view illustrating how a plurality of wires are disposed.

FIG. 17 is a view illustrating a configuration of a TFT substrate according to the present embodiment.

FIG. 18 is a view schematically illustrating a configuration of a TFT substrate (film formation substrate) according to Second Embodiment.

FIG. 19 is a cross-sectional view schematically illustrating a configuration of a conventional vapor deposition device using a shadow mask.

#### DESCRIPTION OF EMBODIMENTS

An embodiment of the present invention is described below with reference to FIGS. 1 through 18.

The present embodiment describes, as an example vapor deposition method involving a vapor deposition device of the present embodiment, a method for producing an organic EL display device that (i) is of a bottom emission type, that is, extracts light from a TFT substrate side, and that (ii) carries out an RGB full color display.

The description first deals with the overall configuration of the organic EL display device.

FIG. 6 is a cross-sectional view schematically illustrating a configuration of the organic EL display device that carries out an RGB full color display. FIG. 7 is a plan view illustrating an arrangement of pixels included in the organic EL display device illustrated in FIG. 6. FIG. 8 is a cross-sectional view, taken long line A-A in FIG. 7, of a TFT substrate included in the organic EL display device illustrated in FIG. 6.

As illustrated in FIG. 6, the organic EL display device 1 produced in the present embodiment includes: a TFT substrate 10 including TFTs 12 (see FIG. 8); organic EL elements 20 provided on the TFT substrate 10 and connected to the TFTs 12; an adhesive layer 30; and a sealing substrate 40, arranged in that order.

As illustrated in FIG. 6, the organic EL elements 20 are contained between the TFT substrate 10 and the sealing substrate 40 by attaching the TFT substrate 10, on which the

organic EL elements **20** are provided, to the sealing substrate **40** with use of the adhesive layer **30**.

According to the organic EL display device **1**, the organic EL elements **20** are thus contained between the TFT substrate **10** and the sealing substrate **40**, and this arrangement prevents infiltration of oxygen, moisture and the like present outside into the organic EL elements **20**.

As illustrated in FIG. **8**, the TFT substrate **10** includes, as a supporting substrate, a transparent insulating substrate **11** such as a glass substrate. The insulating substrate **11** is, as illustrated in FIG. **7**, provided with a plurality of wires **14** including (i) a plurality of gate lines **14G** (see FIG. **12**) laid in the horizontal direction, (ii) a plurality of source lines **14S** (see FIG. **12**) laid in the vertical direction and intersecting with the gate lines **14G**, and (iii) power supply wires **14V** (see FIG. **12**). The gate lines **14G** are connected to a gate line driving circuit (not shown in the drawings) that drives the gate lines **14G**, whereas the signal lines are connected to a signal line driving circuit (not shown in the drawings) that drives the signal lines. How the wires **14** of the TFT substrate **10** of the present embodiment are designed is described later.

The organic EL display device **1** is a full-color, active matrix organic EL display device. The organic EL display device **1** includes, on the insulating substrate **11** and in regions defined by the wires **14**, sub-pixels **2R**, **2G**, and **2B** arranged in a matrix which include organic EL elements **20** of red (R), green (G), and blue (B), respectively.

In other words, the regions defined by the wires **14** each (i) correspond to a single sub-pixel (dot) and (ii) provide a luminescent region of R, G, or B for each sub-pixel.

A pixel **2** (that is, a single pixel) includes three sub-pixels: a red sub-pixel **2R** transmitting red light; a green sub-pixel **2G** transmitting green light; and a blue sub-pixel **2B** transmitting blue light.

The sub-pixels **2R**, **2G**, and **2B** include, as luminescent regions of the respective colors which luminescent regions perform light emission of the respective sub-pixels **2R**, **2G**, and **2B**, openings **15R**, **15G**, and **15B** that are covered respectively by stripe-shaped luminescent layers **23R**, **23G**, and **23B** of the respective colors.

The luminescent layers **23R**, **23G**, and **23B** are each formed in a pattern and color by vapor deposition. Note that the openings **15R**, **15G**, and **15B** will be described later.

The sub-pixels **2R**, **2G**, and **2B** include respective TFTs **12** each connected to a first electrode **21** of a corresponding one of the organic EL elements **20**. The sub-pixels **2R**, **2G**, and **2B** each have an emission intensity that is determined by scan through the wires **14** and selection of the TFTs **12**. As described above, the organic EL display device **1** carries out an image display by selectively causing the organic EL elements **20** to emit, by use of the TFTs **12**, light with desired luminance.

The following describes in detail respective configurations of the TFT substrate **10** and each of the organic EL elements **20** both included in the organic EL display device **1**.

First, the description below deals with the TFT substrate **10**.

The TFT substrate **10**, as illustrated in FIG. **8**, includes on the transparent insulating substrate **11** such as a glass substrate: TFTs **12** (switching elements); an interlayer film **13** (interlayer insulating film, planarizing film); wires **14**; and an edge cover **15**, formed in that order.

The insulating substrate **11** is provided thereon with (i) wires **14** and (ii) pixel driving circuits including TFTs **12** corresponding respectively to the sub-pixels **2R**, **2G**, and **2B**. FIG. **12** is a diagram illustrating a circuit configuration of a pixel driving circuit.

As illustrated in FIG. **12**, the pixel driving circuit includes a transistor Tr1 for control, a transistor Tr2 for driving, and a capacitor C.

A source terminal of the transistor Tr1 is connected to a source line **14S**, a gate terminal of the transistor Tr1 is connected to a gate line **14G**, and a drain terminal of the transistor Tr1 is connected to a gate terminal of the transistor Tr2.

A source terminal of the transistor Tr2 is connected to a power supply wire **14V**, and a drain terminal of the transistor Tr2 is connected to the organic EL element **20**.

The capacitor C is provided between the source terminal of the transistor Tr2 and the gate terminal of the transistor Tr2. The capacitor C is a capacitor for voltage retention.

When data is written into the pixel driving circuit having such a configuration, the gate line **14G** becomes H (High), which causes the transistor Tr1 to turn on. This allows a data voltage signal supplied from the source line **14S** to be written into the capacitor C. Then, the gate line **14G** becomes L (Low), which causes the transistor Tr1 to turn off. This cuts connection between the capacitor C and the source line **14S**, thereby allowing the capacitor C to retain the data voltage signal written therein when data is written into the pixel driving circuit.

An electric current of the transistor Tr2 is determined depending on a voltage between two ends of the capacitor C. Accordingly, an electric current corresponding to the data voltage signal is supplied to the organic EL element.

Each of the pixel driving circuits is not limited to the configuration described above. Each of the pixel driving circuits may, for example, additionally include a circuit for compensating a variation and a change, with passage of time, in properties of the transistors Tr1 and Tr2. Such an additional circuit may necessitate a wire other than the gate line **14G**, the source line **14S**, and the power supply wire **14V**.

The interlayer film **13** is provided on the insulating substrate **11** throughout the entire region of the insulating substrate **11** to cover the TFTs **12**.

There are provided on the interlayer film **13** first electrodes **21** of the organic EL elements **20**.

The interlayer film **13** has contact holes **13a** for electrically connecting the first electrodes **21** of the organic EL elements **20** to the TFTs **12**. This electrically connects the TFTs **12** to the organic EL elements **20** via the contact holes **13a**.

The edge cover **15** is an insulating layer for preventing the first electrode **21** and a second electrode **26** of a corresponding one of the organic EL elements **20** from short-circuiting with each other due to, for example, (i) a reduced thickness of the organic EL layer in an edge section of the pattern of the first electrode **21** or (ii) an electric field concentration.

The edge cover **15** is provided on the interlayer film **13** so as to cover the edge sections of the pattern of the first electrode **21**.

The edge cover **15** has openings **15R**, **15G**, and **15B** for the sub-pixels **2R**, **2G**, and **2B**, respectively. The openings **15R**, **15G**, and **15B** of the edge cover **15** define the respective luminescent regions of the sub-pixels **2R**, **2G**, and **2B**.

The sub-pixels **2R**, **2G**, and **2B** are, in other words, isolated from one another by the insulating edge cover **15**. The edge cover **15** thus functions as an element isolation film as well.

The description below now deals with each of the organic EL elements **20**.

The organic EL element **20** is a light-emitting element capable of high-luminance light emission based on low-voltage direct-current driving, and includes: a first electrode **21**; an organic EL layer; and a second electrode **26**, stacked in that order.

The first electrode **21** is a layer having the function of injecting (supplying) positive holes into the organic EL layer. The first electrode **21** is, as described above, connected to the TFTs **12** via the contact holes **13a**.

The organic EL layer provided between the first electrode **21** and the second electrode **26** includes, as illustrated in FIG. **8**: a hole injection layer/hole transfer layer **22**; luminescent layers **23R**, **23G**, and **23B**; an electron transfer layer **24**; and an electron injection layer **25**, formed in that order from the first electrode **21** side.

The above stack order intends to use (i) the first electrode **21** as an anode and (ii) the second electrode **26** as a cathode. The stack order of the organic EL layer is reversed in the case where the first electrode **21** serves as a cathode and the second electrode **26** serves as an anode.

The hole injection layer has the function of increasing efficiency in injecting positive holes into the luminescent layers **23R**, **23G**, and **23B**. The hole transfer layer has the function of increasing efficiency in transferring positive holes to the luminescent layers **23R**, **23G**, and **23B**. The hole injection layer/hole transfer layer **22** is so formed uniformly throughout the entire display region of the TFT substrate **10** as to cover the first electrode **21** and the edge cover **15**.

The present embodiment describes an example case involving, as the hole injection layer and the hole transfer layer, a hole injection layer/hole transfer layer **22** that integrally combines a hole injection layer with a hole transfer layer as described above. The present embodiment is, however, not limited to such an arrangement: The hole injection layer and the hole transfer layer may be provided as separate layers independent of each other.

There are provided on the hole injection layer/hole transfer layer **22** the luminescent layers **23R**, **23G**, and **23B** so formed in correspondence with the respective sub-pixels **2R**, **2G**, and **2B** as to cover the respective openings **15R**, **15G**, and **15B** of the edge cover **15**.

The luminescent layers **23R**, **23G**, and **23B** are each a layer that has the function of emitting light by recombining (i) holes (positive holes) injected from the first electrode **21** side with (ii) electrons injected from the second electrode **26** side. The luminescent layers **23R**, **23G**, and **23B** are each made of a material with high luminous efficiency, such as a low-molecular fluorescent dye and a metal complex.

The electron transfer layer **24** is a layer that has the function of increasing efficiency in transferring electrons from the second electrode **26** to the luminescent layers **23R**, **23G**, and **23B**. The electron injection layer **25** is a layer that has the function of increasing efficiency in injecting electrons from the second electrode **26** into the electron transfer layer **24**.

The electron transfer layer **24** is so provided on the luminescent layers **23R**, **23G**, and **23B** and the hole injection layer/hole transfer layer **22** uniformly throughout the entire display region of the TFT substrate **10** as to cover the luminescent layers **23R**, **23G**, and **23B** and the hole injection layer/hole transfer layer **22**. The electron injection layer **25** is so provided on the electron transfer layer **24** uniformly throughout the entire display region of the TFT substrate **10** as to cover the electron transfer layer **24**.

The electron transfer layer **24** and the electron injection layer **25** may be provided either (i) as separate layers independent of each other as described above or (ii) integrally with each other. In other words, the organic EL display device may include an electron transfer layer/electron injection layer instead of the electron transfer layer **24** and the electron injection layer **25**.

The second electrode **26** is a layer having the function of injecting electrons into the organic EL layer including the

above organic layers. The second electrode **26** is so provided on the electron injection layer **25** uniformly throughout the entire display region of the TFT substrate **10** as to cover the electron injection layer **25**.

The organic layers other than the luminescent layers **23R**, **23G**, and **23B** are not essential for the organic EL layer, and may thus be included as appropriate in accordance with a required property of the organic EL element **20**. The organic EL layer may further include a carrier blocking layer according to need. The organic EL layer can, for example, additionally include, as a carrier blocking layer, a hole blocking layer between the luminescent layers **23R**, **23G**, and **23B** and the electron transfer layer **24** to prevent positive holes from transferring from the luminescent layers **23R**, **23G**, and **23B** to the electron transfer layer **24** and thus to improve luminous efficiency.

The organic EL element **20** can have, for example, any of the layered structures (1) through (8) below:

- (1) first electrode/luminescent layer/second electrode
- (2) first electrode/hole transfer layer/luminescent layer/electron transfer layer/second electrode
- (3) first electrode/hole transfer layer/luminescent layer/hole blocking layer (carrier blocking layer)/electron transfer layer/second electrode
- (4) first electrode/hole transfer layer/luminescent layer/hole blocking layer/electron transfer layer/electron injection layer/second electrode
- (5) first electrode/hole injection layer/hole transfer layer/luminescent layer/electron transfer layer/electron injection layer/second electrode
- (6) first electrode/hole injection layer/hole transfer layer/luminescent layer/hole blocking layer/electron transfer layer/second electrode
- (7) first electrode/hole injection layer/hole transfer layer/luminescent layer/hole blocking layer/electron transfer layer/electron injection layer/second electrode
- (8) first electrode/hole injection layer/hole transfer layer/electron blocking layer (carrier blocking layer)/luminescent layer/hole blocking layer/electron transfer layer/electron injection layer/second electrode

As described above, the hole injection layer and the hole transfer layer, for example, may be integrated with each other. The electron transfer layer and the electron injection layer may be integrated with each other.

The structure of the organic EL element **20** is not limited to the above example layered structure, and may be a desired layered structure according to a required property of the organic EL element **20** as described above.

The description below deals with a method for producing the organic EL display device **1**.

FIG. **9** is a flowchart indicating successive steps for producing the organic EL display device **1**.

As illustrated in FIG. **9**, the method of the present embodiment for producing the organic EL display device **1** includes steps such as a TFT substrate and first electrode preparing step (S1), a hole injection layer/hole transfer layer vapor deposition step (S2), a luminescent layer vapor deposition step (S3), an electron transfer layer vapor deposition step (S4), an electron injection layer vapor deposition step (S5), a second electrode vapor deposition step (S6), and a sealing step (S7).

The following describes, with reference to the flowchart illustrated in FIG. **9**, the individual steps described above with reference to FIGS. **7** and **8**.

Note, however, that the dimensions, materials, shapes and the like of the respective constituent elements described in the present embodiment merely serve as an embodiment, and that

the scope of the present invention should not be construed limitedly on the grounds of such aspects of the constituent elements.

The stack order described in the present embodiment, as mentioned above, intends to use (i) the first electrode **21** as an anode and (ii) the second electrode **26** as a cathode. In the converse case where the first electrode **21** serves as a cathode and the second electrode **26** serves as an anode, the stack order of the organic EL layer is reversed, and the respective materials of the first electrode **21** and the second electrode **26** are switched similarly.

First, as illustrated in FIG. 8, the method of the present embodiment (i) applies a photosensitive resin onto an insulating substrate **11** that is made of a material such as glass and that includes, for example, TFTs **12** and wires **14** each formed by a publicly known technique, and (ii) carries out patterning with respect to the photosensitive resin by photolithography. This forms an interlayer film **13** on the insulating substrate **11**.

The insulating substrate **11** is, for example, a glass or plastic substrate having (i) a thickness of 0.7 to 1.1 mm, (ii) a length (longitudinal length) of 400 to 500 mm along a y axis direction, and (iii) a length (lateral length) of 300 to 400 mm along an x axis direction. The insulating substrate **11** of the present embodiment was a glass substrate.

The interlayer film **13** can be made of, for example, an acrylic resin or a polyimide resin. The acrylic resin is, for example, a product in the Optomer series available from JSR Corporation. The polyimide resin is, for example, a product in the Photoneece series available from Toray Industries, Inc. Note that since a typical polyimide resin is not transparent but colored, the interlayer film **13** is more suitably made of a transparency resin such as an acrylic resin in the case where an organic EL display device of the bottom emission type is produced as the organic EL display device **1** as illustrated in FIG. 8.

The interlayer film **13** is simply required to have a film thickness that can compensate for the difference in level created by the TFTs **12**. The film thickness is thus not particularly limited. The film thickness was, for example, approximately 2  $\mu\text{m}$  in the present embodiment.

The method of the present embodiment next forms, in the interlayer film **13**, contact holes **13a** for electrically connecting the first electrode **21** to the TFTs **12**.

The method then forms, as a conductive film (electrode film), a film such as an ITO (indium tin oxide) film by a method such as a sputtering method so that the film has a thickness of 100 nm.

The method next applies a photoresist onto the ITO film, carries out patterning with respect to the photoresist by photolithography, and then carries out etching with respect to the ITO film with use of ferric chloride as an etchant. The method then strips the photoresist with use of a resist exfoliative solution, and washes the substrate. This forms, on the interlayer film **13**, a first electrode **21** in a matrix.

The conductive film material for the first electrode **21** is, for example, (i) a transparent conductive material such as ITO, IZO (indium zinc oxide), and gallium-added zinc oxide (GZO) or (ii) a metal material such as gold (Au), nickel (Ni), and platinum (Pt).

The above conductive film can be formed by, instead of the sputtering method, a method such as a vacuum vapor deposition method, a chemical vapor deposition (CVD) method, a plasma CVD method, and a printing method.

The thickness of the first electrode **21** is not particularly limited. The first electrode **21** can have a thickness of, for example, 100 nm as mentioned above.

The method next forms a pattern of an edge cover **15**, as with the interlayer film **13**, to have a film thickness of, for example, approximately 1  $\mu\text{m}$ . The edge cover **15** can be made of an insulating material similar to that for the interlayer film **13**.

The step described above prepares the TFT substrate **10** and the first electrode **21** (S1).

The method of the present embodiment next carries out, with respect to the TFT substrate **10** prepared through the above step, (i) a bake under a reduced pressure for dehydration and (ii) an oxygen plasma treatment for surface washing of the first electrode **21**.

The method then carries out vapor deposition of a hole injection layer and a hole transfer layer (in the present embodiment, a hole injection layer/hole transfer layer **22**) on the TFT substrate **10** throughout its entire display region with use of a conventional vapor deposition device (S2).

Specifically, the method (i) carries out an alignment adjustment, relative to the TFT substrate **10**, of an open mask having an opening corresponding to the entire display region and (ii) closely attaches the open mask to the TFT substrate **10**. The method then, while rotating the TFT substrate **10** and the open mask together, carries out, through the opening of the open mask and uniformly throughout the entire display region, vapor deposition of vapor deposition particles scattered from a vapor deposition source.

The above vapor deposition carried out throughout the entire display region refers to vapor deposition carried out unintermittently over sub-pixels having different colors and located adjacent to one another.

The hole injection layer and the hole transfer layer are each made of a material such as (i) benzine, styryl amine, triphenylamine, porphyrin, triazole, imidazole, oxadiazole, pol-yarylalkane, phenylenediamine, arylamine, oxazole, anthracene, fluorenone, hydrazone, stilbene, triphenylene, azatriphenylene, or a derivative of any of the above, (ii) a polysilane compound, (iii) a vinylcarbazole compound, (iv) and a monomer, an oligomer, or a polymer of an open chain conjugated system, such as a thiophene compound and an aniline compound.

The hole injection layer and the hole transfer layer may be either integrated with each other as described above or formed as separate layers independent of each other. The hole injection layer and the hole transfer layer each have a film thickness of, for example, 10 to 100 nm.

The present embodiment used, as the hole injection layer and the hole transfer layer, a hole injection layer/hole transfer layer **22** that was made of 4,4'-bis[N-(1-naphthyl)-N-phenylamino]biphenyl( $\alpha$ -NPD) and that had a film thickness of 30 nm.

The method of the present embodiment next carries out a selective application formation (pattern formation) of luminescent layers **23R**, **23G**, and **23B** on the hole injection layer/hole transfer layer **22** in correspondence with respective sub-pixels **2R**, **2G**, and **2B** so that the luminescent layers **23R**, **23G**, and **23B** cover respective openings **15R**, **15G**, and **15B** of the edge cover **15** (S3).

As described above, the luminescent layers **23R**, **23G**, and **23B** are each made of a material with high luminous efficiency, such as a low-molecular fluorescent dye and a metal complex.

The luminescent layers **23R**, **23G**, and **23B** are each made of a material such as (i) anthracene, naphthalene, indene, phenanthrene, pyrene, naphthacene, triphenylene, anthracene, perylene, picene, fluoranthene, accephenanthrylene, pentaphene, pentacene, coronene, butadiene, coumarin, acridine, stilbene, or a derivative of any of the above,

(ii) a tris(8-hydroxyquinolate) aluminum complex, (iii) a bis(benzohydroxyquinolate) beryllium complex, (iv) a tri(dibenzoylmethyl)phenanthroline europium complex, (v) and ditoluoyl vinyl biphenyl.

The luminescent layers **23R**, **23G**, and **23B** each have a film thickness of, for example, 10 to 100 nm.

The vapor deposition method and the vapor deposition device of the present embodiment are each particularly suitably used for a selective application formation (pattern formation) of such luminescent layers **23R**, **23G**, and **23B**.

A description below deals in detail with a selective application formation of the luminescent layers **23R**, **23G**, and **23B** which selective application formation involves the vapor deposition method and the vapor deposition device of the present embodiment.

The method of the present embodiment next carries out, in a manner similar to that described for the above hole injection layer/hole transfer layer vapor deposition step (S2), vapor deposition of an electron transfer layer **24** throughout the entire display region of the TFT substrate **10** so that the electron transfer layer **24** covers the hole injection layer/hole transfer layer **22** and the luminescent layers **23R**, **23G**, and **23B** (S4).

The method then carries out, in a manner similar to that described for the above hole injection layer/hole transfer layer vapor deposition step (S2), vapor deposition of an electron injection layer **25** throughout the entire display region of the TFT substrate **10** so that the electron injection layer **25** covers the electron transfer layer **24** (S5).

The electron transfer layer **24** and the electron injection layer **25** are each made of a material such as a tris(8-hydroxyquinolate) aluminum complex, an oxadiazole derivative, a triazole derivative, a phenylquinoxaline derivative, or a silole derivative.

Specific examples of the material include (i) Alq(tris(8-hydroxy quinoline)aluminum), anthracene, naphthalene, phenanthrene, pyrene, anthracene, perylene, butadiene, coumarin, acridine, stilbene, 1,10-phenanthroline, and a derivative or metal complex of any of the above, and (ii) LiF.

As mentioned above, the electron transfer layer **24** and the electron injection layer **25** may be either integrated with each other or formed as separate layers independent of each other. The electron transfer layer **24** and the electron injection layer **25** each have a film thickness of, for example, 1 to 100 nm. The respective film thicknesses of the electron transfer layer **24** and the electron injection layer **25** add up to, for example, 20 to 200 nm.

In the present embodiment, (i) the electron transfer layer **24** was made of Alq, whereas the electron injection layer **25** was made of LiF, and (ii) the electron transfer layer **24** had a film thickness of 30 nm, whereas the electron injection layer **25** had a film thickness of 1 nm.

The method of the present embodiment next carries out, in a manner similar to that described for the above hole injection layer/hole transfer layer vapor deposition step (S2), vapor deposition of a second electrode **26** throughout the entire display region of the TFT substrate **10** so that the second electrode **26** covers the electron injection layer **25** (S6).

The second electrode **26** is suitably made of a material (electrode material) such as a metal with a small work function. Examples of such an electrode material include a magnesium alloy (for example, MgAg), an aluminum alloy (for example, AlLi, AlCa, or AlMg) and calcium metal. The second electrode **26** has a thickness of, for example, 50 to 100 nm.

In the present embodiment, the second electrode **26** was made of aluminum and has a film thickness of 50 nm. The

operation described above forms, on the TFT substrate **10**, organic EL elements **20** each including the organic EL layer, the first electrode **21**, and the second electrode **26** described above.

The method of the present embodiment then attached (i) the TFT substrate **10**, on which the organic EL elements **20** are provided, to (ii) a sealing substrate **40** with use of an adhesive layer **30** as illustrated in FIG. 6 so that the organic EL elements **20** were contained.

The sealing substrate **40** is, for example, an insulating substrate such as a glass substrate and a plastic substrate and 0.4 to 1.1 mm in thickness. The sealing substrate **40** of the present embodiment was a glass substrate.

The longitudinal and lateral lengths of the sealing substrate **40** may each be adjusted as appropriate in accordance with the size of a target organic EL display device **1**. The sealing substrate **40** may be an insulating substrate substantially equal in size to the insulating substrate **11** of the TFT substrate **10**, in which case a combination of the sealing substrate **40**, the TFT substrate **10**, and the organic EL elements **20** contained therebetween is divided in accordance with the size of a target organic EL display device **1**.

The method for containing the organic EL elements **20** is not limited to the method described above. Examples of other containing methods include (i) a method that uses a centrally depressed glass substrate as the sealing substrate **40** and that the combination of the sealing substrate **40** and the TFT substrate **10** is sealed along the edge in a frame shape with use of, for example, a sealing resin or fritted glass, and (ii) a method that fills a space between the TFT substrate **10** and the sealing substrate **40** with a resin. The method for producing the organic EL display device **1** does not depend on the above containing method, and can employ any of various containing methods.

The second electrode **26** may be provided thereon with a protective film (not shown) that covers the second electrode **26** and that prevents infiltration of oxygen, moisture and the like present outside into the organic EL elements **20**.

The protective film is made of an electrically insulating or conductive material such as silicon nitride and silicon oxide. The protective film has a thickness of, for example, 100 to 1000 nm.

Through the above steps, the organic EL display device **1** is finally produced.

The organic EL display device **1**, upon receipt of a signal through a wire **14**, turns on a TFT **12** (turns on both a transistor Tr1 and a transistor Tr2) and thus allows (i) positive holes to be injected from the first electrode **21** into the organic EL layer and further (ii) electrons to be injected from the second electrode **26** into the organic EL layer. This causes the positive holes and the electrons to recombine with each other inside the luminescent layers **23R**, **23G**, and **23B**. The positive holes and the electrons thus recombined are emitted in the form of light when becoming inactive.

In the above organic EL display device **1**, controlling respective light emission luminances of the sub-pixels **2R**, **2G**, and **2B** allows a predetermined image to be displayed.

The following describes an arrangement of a vapor deposition device of the present embodiment.

FIG. 1 is a plan view of a film formation substrate and a mask unit both inside a vacuum chamber of the vapor deposition device of the present embodiment, the plan view being taken from a back surface side of the film formation substrate (that is, the side opposite to the vapor-deposited surface). For convenience of illustration, FIG. 1 uses a chain double-dashed line to represent the film formation substrate. FIG. 2 is a bird's eye view of main constituent elements inside the

vacuum chamber of the vapor deposition device of the present embodiment. FIG. 3 is a cross-sectional view schematically illustrating a configuration of a main part of the vapor deposition device of the present embodiment. FIG. 3 illustrates a cross section of the vapor deposition device, the cross section being taken along line B-B of FIG. 1. FIG. 4 is a block diagram illustrating a part of a configuration of the vapor deposition device of the present embodiment.

The vapor deposition device 50 of the present embodiment, as illustrated in FIG. 3, includes: a vacuum chamber 60 (film growing chamber); a substrate moving mechanism 70 (substrate moving means; moving means); a mask unit 80; image sensors 90; and a control circuit 100 (see FIG. 4).

As illustrated in FIG. 3, the vacuum chamber 60 contains the substrate moving mechanism 70 and the mask unit 80.

The vacuum chamber 60 is provided with a vacuum pump (not shown) for vacuum-pumping the vacuum chamber 60 via an exhaust port (not shown) of the vacuum chamber 60 to keep a vacuum in the vacuum chamber 60 during vapor deposition.

The substrate moving mechanism 70 includes, for example: a substrate holding member 71 (substrate holding means) for holding a film formation substrate 200 (for example, a TFT substrate 10); and a motor 72 (see FIG. 4).

The substrate moving mechanism 70 causes (i) the substrate holding member 71 to hold the film formation substrate 200 and (ii) a below-described motor drive control section 103 (see FIG. 4) to drive the motor 72 so as to hold the film formation substrate 200 and move it in the horizontal direction. The substrate moving mechanism 70 may be provided to be capable of moving the film formation substrate 200 either (i) in both the x axis direction and the y axis direction or (ii) in one of the x axis direction and the y axis direction.

The substrate holding member 71 is an electrostatic chuck. The film formation substrate 200 is, in a state in which bend due to its own weight is absent, so held by the electrostatic chuck as to be separated from a below-described shadow mask 81 of the mask unit 80 by a fixed gap g1 (void; vertical distance).

The gap g1 between the film formation substrate 200 and the shadow mask 81 preferably falls within the range of not less than 50  $\mu\text{m}$  and not more than 3 mm, or is more preferably on the order of 200  $\mu\text{m}$ .

If the gap g1 is smaller than 50  $\mu\text{m}$ , the film formation substrate 200 will likely be come into contact with the shadow mask 81.

If the gap g1 is larger than 3 mm, vapor deposition particles that have passed through openings 82 of the shadow mask 81 are spread widely, which results in a vapor-deposited film 211 being formed to have too large a pattern width. In the case where, for example, the vapor-deposited film 211 is the luminescent layer 23R, the gap g1 being larger than 3 mm may undesirably result in vapor deposition of the material of the luminescent layer 23R through the respective openings 15G and 15B of the adjacent sub-pixels 2G and 2B.

With the gap g1 being approximately 200  $\mu\text{m}$ , (i) there is no risk of the film formation substrate 200 coming into contact with the shadow mask 81, and (ii) the vapor-deposited film 211 can have a sufficiently small pattern width.

The mask unit 80, as illustrated in FIG. 3, includes: a shadow mask 81 (vapor deposition mask, mask); a vapor deposition source 85; a mask holding member 87 (holding means); a mask tension mechanism 88; and a shutter 89 (see FIG. 4).

The shadow mask 81 is, for example, a metal mask.

The shadow mask 81 is so formed as to (i) be smaller in area than a vapor deposition region 210 of the film formation

substrate 200 and (ii) have at least one side that is shorter than the width of the vapor deposition region 210 of the film formation substrate 200.

The shadow mask 81 of the present embodiment has a rectangular shape (that is, in the shape of a belt), and is sized as follows: The shadow mask 81 is, as illustrated in FIG. 1, so formed as to have (i) long sides 81a each with a width d1 (that is, the length along the long-side direction [long-axis direction] of the shadow mask 81) that is larger than the width d3 of a side of the vapor deposition region 210 (in the example illustrated in FIG. 1, a long side 210a of the vapor deposition region 210) which side faces the long sides 81a of the shadow mask 81 and (ii) short sides 81b each with a width d2 (that is, the length along the short-side direction [short-axis direction] of the shadow mask 81) that is smaller than the width d4 of a side of the vapor deposition region 210 (in the example illustrated in FIG. 1, a short side 210b of the vapor deposition region 210) which side faces the short sides 81b of the shadow mask 81.

The shadow mask 81, as illustrated in FIGS. 1 and 2, has a plurality of openings 82 (through holes) arranged in a one-dimensional direction and each having the shape of, for example, a belt (that is, in a stripe shape). In the case where, for example, a selective application formation of the luminescent layers 23R, 23G, and 23B is carried out with respect to the TFT substrate 10 as a pattern formation of vapor-deposited films 211 (see FIG. 3) on the film formation substrate 200, the openings 82 are formed in correspondence with the size and pitch of columns for each color of the luminescent layers 23R, 23G, and 23B.

The shadow mask 81, as illustrated in FIG. 1, includes, for example, alignment marker sections 83 extending along a scanning direction (substrate scanning direction) of the film formation substrate 200. The alignment marker sections 83 include respective alignment markers 84 (see FIG. 3) for use in an alignment between the film formation substrate 200 and the shadow mask 81.

The alignment marker sections 83 of the present embodiment are, as illustrated in FIG. 1, provided along the short sides 81b (short axis) of the shadow mask 81.

The shadow mask 81, as described above, has (i) long sides 81a each with a width d1 that is larger than the width d3 of a side of the vapor deposition region 210 which side faces the long sides 81a and (ii) short sides 81b each with a width d2 that is smaller than the width d4 of a side of the vapor deposition region 210 which side faces the short sides 81b. This arrangement allows the alignment marker sections 83 to be formed respectively in opposite end sections arranged along the long-side direction (that is, at the opposite short sides 81b and 81b). The above arrangement thus makes it possible to carry out an alignment easily and more precisely.

The film formation substrate 200, as illustrated in FIG. 1, includes alignment marker sections 220 outside the vapor deposition region 210 and along the scanning direction (substrate scanning direction) of the film formation substrate 200. The alignment marker sections 220 include respective alignment markers 221 (see FIG. 3) for use in an alignment between the film formation substrate 200 and the shadow mask 81.

The alignment marker sections 220 of the present embodiment are, as illustrated in FIG. 1, provided along the respective short sides 210b (short axis) of the vapor deposition region 210 of the film formation substrate 200.

The stripe-shaped openings 82 of the present embodiment are provided to (i) extend along the short side direction of the shadow mask 81, that is, the substrate scanning direction, and to (ii) be arranged next to one another along the long side

direction of the shadow mask **81**, that is, a direction that orthogonally crosses the substrate scanning direction.

The vapor deposition source **85** is, for example, a container that contains a vapor deposition material. The vapor deposition source **85** is, as illustrated in FIGS. **1** through **3**, (i) placed to face the shadow mask **81** and (ii) separated from the shadow mask **81** by a fixed gap **g2** (void), that is, positioned away from the shadow mask **81** by a fixed distance.

The vapor deposition source **85** may be a container that itself contains a vapor deposition material or a container that includes a load-lock pipe.

The vapor deposition source **85** includes, for example, a mechanism for emitting vapor deposition particles upward.

The vapor deposition source **85** has, on a surface facing the shadow mask **81**, a plurality of injection holes **86** for emitting (scattering) the vapor deposition material in the form of vapor deposition particles.

The present embodiment is arranged, as described above, such that (i) the vapor deposition source **85** is provided below the film formation substrate **200** and that (ii) the film formation substrate **200** is held by the substrate holding member **71** in such a state that the vapor deposition region **210** faces downward. Thus, in the present embodiment, the vapor deposition source **85** carries out vapor deposition of vapor deposition particles through the openings **82** of the shadow mask **81** onto the film formation substrate **200** upward from below (that is, up deposition; hereinafter referred to as "depo-up").

The injection holes **86** are, as illustrated in FIGS. **1** and **2**, provided to face the respective openings **82** of the shadow mask **81** so as to be open in respective opening regions of the shadow mask **81**. The injection holes **86** of the present embodiment are arranged one-dimensionally (i) along the direction in which the openings **82** of the shadow mask **81** are arranged next to one another and (ii) so as to face the respective openings **82** of the shadow mask **81**.

Thus, as illustrated in FIGS. **1** and **2**, the vapor deposition source **85** is formed to have a surface that faces the shadow mask **81**, the surface (that is, the surface in which the injection holes **86** are provided) having, for example, a rectangular shape (belt shape) as viewed from the back surface side of the film formation substrate **200** (that is, in a plan view) so as to match the rectangular shape (belt shape) of the shadow mask **81**.

In the mask unit **80**, the shadow mask **81** and the vapor deposition source **85** are fixed in position relative to each other. Specifically, there is constantly a fixed gap **g2** between (i) the shadow mask **81** and (ii) the surface of the vapor deposition source **85** in which surface the injection holes **86** are provided, and there is constantly a fixed positional relationship between (i) the openings **82** of the shadow mask **81** and (ii) the injection holes **86** of the vapor deposition source **85**.

The injection holes **86** of the vapor deposition source **85** are each so placed as to coincide with the center of a corresponding opening **82** of the shadow mask **81** when the mask unit **80** is viewed from the back surface side of the film formation substrate **200** (that is, in a plan view).

The shadow mask **81** and the vapor deposition source **85** are, for example, attached to the mask holding member **87** (for example, an identical holder) for holding and fixing (i) the shadow mask **81** via the mask tension mechanism **88** and (ii) the vapor deposition source **85** (see FIG. **3**). The shadow mask **81** and the vapor deposition source **85** are thus so integrated with each other as to be held and fixed in the respective positions relative to each other.

The shadow mask **81** is under tension caused by the mask tension mechanism **88**. The shadow mask **81** is thus adjusted as appropriate so that no bend or elongation due to its own weight is caused.

The vapor deposition device **50** is arranged as described above such that (i) the film formation substrate **200** is adhered by suction to a fixing plate by the substrate holding member **71** (electrostatic chuck), and is thus prevented from being bent due to its own weight and (ii) the shadow mask **81** is under tension caused by the mask tension mechanism **88** so that the distance between the film formation substrate **200** and the shadow mask **81** is uniformly maintained throughout the entire region by which the film formation substrate **200** overlaps the shadow mask **81** in a plan view.

The shutter **89** is used according to need in order to control reaching of vapor deposition particles to the shadow mask **81**. The shutter **89** is either closed or opened by a shutter drive control section **105** (see FIG. **4**) in accordance with a vapor deposition OFF signal or vapor deposition ON signal from a vapor deposition ON/OFF control section **104** (see FIG. **4**) described below.

The shutter **89** is, for example, provided to be capable of moving in a space between the shadow mask **81** and the vapor deposition source **85** (that is, capable of being inserted between them). The shutter **89** is inserted between the shadow mask **81** and the vapor deposition source **85** to close the openings **82** of the shadow mask **81**.

The vapor deposition device **50** is so adjusted that vapor deposition particles from the vapor deposition source **85** are scattered below the shadow mask **81**. The vapor deposition device **50** may be arranged such that vapor deposition particles scattered beyond the shadow mask **81** are blocked as appropriate by, for example, a deposition preventing plate (shielding plate).

The vacuum chamber **60** is provided with, for example, image sensors **90** (see FIG. **4**) each (i) attached to an outer surface of the vacuum chamber **60**, (ii) including a CCD, and (iii) serving as image sensing means (image reading means). The vacuum chamber **60** is further provided with a control circuit **100** (i) attached to the outer surface of the vacuum chamber **60**, (ii) connected to the image sensors **90**, and (iii) serving as control means.

The image sensors **90** each function as position detecting means for use in an alignment of the film formation substrate **200** and the shadow mask **81**.

The control circuit **100** includes: an image detecting section **101**; a computing section **102**; a motor drive control section **103**; a vapor deposition ON/OFF control section **104**; and a shutter drive control section **105**.

As described above, the film formation substrate **200** includes, as illustrated in FIG. **1**, alignment marker sections **220** provided (i) outside the vapor deposition region **210** and (ii) along, for example, the substrate scanning direction. The alignment marker sections **220** each include an alignment marker **221**.

The image detecting section **101** detects, on the basis of an image captured by the image sensors **90**, respective images of (i) the alignment markers **221** included in the film formation substrate **200** and (ii) the alignment markers **84** of the shadow mask **81**. The image detecting section **101** further detects the start end and rear end of the vapor deposition region **210** of the film formation substrate **200** on the basis of, among the alignment markers **221** included in the film formation substrate **200**, (i) a start-end marker indicative of the start end of the vapor deposition region **210** and (ii) a rear-end marker indicative of the rear end of the vapor deposition region **210**.

The start-end marker and the rear-end marker mentioned above may be identical to each other. In this case, the image detecting section 101 detects, with respect to the substrate scanning direction, whether a particular end of the vapor deposition region 210 is its start end or rear end.

The computing section 102 determines, from the image detected by the image detecting section 101, the amount of movement of the film formation substrate 200 and the shadow mask 81 relative to each other (for example, the amount of movement of the film formation substrate 200 relative to the shadow mask 81). The computing section 102, for example, measures the amount of positional difference (that is, a shift component along the x axis direction and the y axis direction, and a rotation component on the x-y plane) between the alignment markers 221 and the alignment markers 84 to determine a correction value for a substrate position of the film formation substrate 200 by computation. In other words, the computing section 102 determines the correction value by computation with respect to (i) the direction perpendicular to the substrate scanning direction and (ii) a rotation direction of the film formation substrate 200.

The rotation direction of the film formation substrate refers to a direction of rotation on the x-y plane about a z axis, serving as a rotation axis, at the center of a film formation surface of the film formation substrate 200.

The correction value is outputted in the form of a correction signal to the motor drive control section 103. The motor drive control section 103, on the basis of the correction signal from the computing section 102, drives the motor 72 connected to the substrate holding member 71, and thus corrects the substrate position of the film formation substrate 200.

How the substrate position is corrected with use of the alignment markers 84 and 221 is described below together with example shapes of the alignment markers 84 and 221.

The motor drive control section 103 drives the motor 72 to move the film formation substrate 200 in the horizontal direction as mentioned above.

The vapor deposition ON/OFF control section 104 generates (i) a vapor deposition OFF signal when the image detecting section 101 detects the rear-end of the vapor deposition region 210 and (ii) a vapor deposition ON signal when the image detecting section 101 detects the start-end of the vapor deposition region 210.

The shutter drive control section 105 (i) closes the shutter 89 upon receipt of a vapor deposition OFF signal from the vapor deposition ON/OFF control section 104 and (ii) opens the shutter 89 upon receipt of a vapor deposition ON signal from the vapor deposition ON/OFF control section 104.

The following describes (i) how the substrate position is corrected with use of the alignment markers 84 and 221 and (ii) example shapes of the alignment markers 84 and 221.

(a) through (c) of FIG. 5 illustrate example shapes of the alignment markers 84 and 221. (b) and (c) of FIG. 5 each illustrate only two of the juxtaposed alignment markers 84 and of the juxtaposed alignment markers 221 for convenience of illustration.

The computing section 102, on the basis of an image of the alignment markers 84 and 221, the image having been detected by the image detecting section 101, measures (determines) (i) a distance r between respective ends (outer edges) of each alignment marker 84 and its corresponding alignment marker 221 along the x axis direction and (ii) a distance q between respective ends (outer edges) of each alignment marker 84 and its corresponding alignment marker 221 along the y axis direction. The computing section 102 thus determines the amount of positional difference in alignment to compute a correction value for a substrate position.

In the case where, for example, the substrate scanning direction is the x axis direction, the sign "r" in (a) through (c) of FIG. 5 indicates a distance between the respective ends along the substrate scanning direction, whereas the sign "q" in (a) through (c) of FIG. 5 indicates a distance between the respective ends along the direction perpendicular to the substrate scanning direction. The computing section 102 measures (determines) the distances r and q at, for example, opposite ends of the vapor deposition region 210 of the film formation substrate 200 to determine the amount of shift caused in alignment during a substrate scan.

The present embodiment describes an example case that involves simultaneously scanning the film formation substrate 200 and carrying out an alignment between the shadow mask 81 and the film formation substrate 200 as described below. The present embodiment is, however, not limited to such an arrangement. The present embodiment can alternatively be arranged such that a sufficient alignment is carried out before a substrate scan and that no alignment is carried out during a substrate scan.

The present embodiment can be arranged as in an embodiment described below such that, for example, the film formation substrate 200 is moved along a first side of the vapor deposition region 210 of the film formation substrate 200 (for example, along the y axis direction in (a) through (c) of FIG. 5), and is then moved along a second side (for example, the x axis direction in (a) through (c) of FIG. 5) orthogonal to the first side. In this case, the sign "r" in (a) through (c) of FIG. 5 indicates a distance between the respective ends along the direction perpendicular to the substrate scanning direction, whereas the sign "q" in (a) through (c) of FIG. 5 indicates a distance between the respective ends along the direction (shift direction) in which the film formation substrate 200 is moved.

In this case, the computing section 102 measures distances r and q for alignment markers located at the four corners, and thus determines (i) the amount of positional difference present in alignment at the start of a substrate scan and (ii) the amount of positional difference present in alignment after the film formation substrate 200 is moved (shifted).

The alignment markers 84 and 221 may each be, as illustrated in (a) through (c) of FIG. 5, in the shape of, for example, (i) a belt, (ii) a rectangle such as a square, (iii) a frame, or (iv) a cross. The alignment markers 84 and 221 are thus not particularly limited in terms of shape.

In the case where a sufficient alignment is carried out before a substrate scan and no alignment is carried out during a substrate scan as described above, the alignment markers 221 do not need to be provided along a side of the vapor deposition region 210 of the film formation substrate 200, and may instead be provided at, for example, the four corners of the film formation substrate 200.

The following describes in detail a method for forming a pattern of an organic EL layer by using, as a device for producing the organic EL display device 1, the above vapor deposition device 50 of the present embodiment.

The description below deals with an example case that, as described above, involves (i) using, as the film formation substrate 200, a TFT substrate 10 obtained after the hole injection layer/hole transfer layer vapor deposition step (S2) is finished and (ii) carrying out, as a pattern formation of an organic EL layer, a selective application formation of luminescent layers 23R, 23G, and 23B during the luminescent layer vapor deposition step (S3).

The present embodiment assumed (i) 100 mm for the gap g2 between the vapor deposition source 85 and the shadow mask 81 (that is, the distance between a surface of the vapor deposition source 85 in which surface the injection holes 86

are provided and the shadow mask **81**) and (ii) 200  $\mu\text{m}$  for the distance between the TFT substrate **10** serving as the film formation substrate **200** and the shadow mask **81**.

The present embodiment further assumed (i) for a substrate size of the TFT substrate **10**, 320 mm along the scanning direction and 400 mm along the direction perpendicular to the scanning direction and (ii) for widths of the vapor deposition region (display region), 260 mm for the width along the scanning direction (that is, the width **d4**) and 310 mm for the width (that is, the width **d3**) along the direction perpendicular to the scanning direction.

The present embodiment assumed 360  $\mu\text{m}$  (along the scanning direction) $\times$ 90  $\mu\text{m}$  (along the direction perpendicular to the scanning direction) for widths of the openings **15R**, **15G**, and **15B** for the respective sub-pixels **2R**, **2G**, and **2B** of the TFT substrate **10**. The present embodiment further assumed 480  $\mu\text{m}$  (along the scanning direction) $\times$ 160  $\mu\text{m}$  (along the direction perpendicular to the scanning direction) for a pitch between the openings **15R**, **15G**, and **15B**. The pitch between the openings **15R**, **15G**, and **15B** (that is, a pitch between pixel openings) refers to a pitch between respective openings **15R**, **15G**, and **15B** for the sub-pixels **2R**, **2G**, and **2B** adjacent to one another, but not to a pitch between sub-pixels of an identical color.

The present embodiment used, as the shadow mask **81**, a shadow mask having (i) a length of 600 mm along the width **d1** (that is, the width along the direction perpendicular to the scanning direction) along each long side **81a** (corresponding to the long-axis direction) and (ii) a length of 200 mm along the width **d2** (that is, the width along the scanning direction) along each short side **81b** (corresponding to the short-axis direction). The shadow mask **81** had openings **82** (i) each having opening widths of 150 mm (along the width **d5** in the long-axis direction; see FIG. 1) $\times$ 130  $\mu\text{m}$  (along the width **d6** in the short-axis direction; see FIG. 1), (ii) having, along an interval **d8** (see FIG. 1) between adjacent openings **82** and **82**, a length of 350  $\mu\text{m}$ , and (iii) having, along a pitch **p** (see FIG. 1) between respective centers of adjacent openings **82** and **82**, a length of 480  $\mu\text{m}$ .

In the present embodiment, the shadow mask **81** preferably has a length of not less than 200 mm for the width **d2** (that is, a short side length) along each short side **81b**. This is due to the reason below.

The vapor deposition rate is preferably not higher than 10 nm/s. If the vapor deposition rate exceeds 10 nm/s, a deposited film (that is, a vapor-deposited film) will have a decreased uniformity, thus resulting in a decreased organic EL property.

A vapor-deposited film typically has a film thickness of not larger than 100 nm. A film thickness of larger than 100 nm will require application of a high voltage, and consequently increase power consumption of a produced organic EL display device. The above vapor deposition rate and the film thickness of a vapor-deposited film allow estimation of a necessary vapor deposition period of 10 seconds.

Due to a limit in processing capability (tact time), a scan rate of 13.3 mm/s or higher is at least necessary in order to, for example, complete vapor deposition with respect to a 2 m-wide glass substrate in 150 seconds. The processing time of 150 seconds is a tact time that allows processing of about 570 glass substrates per day.

Securing the above vapor deposition period of 10 seconds at the above scan rate requires the shadow mask **81** to have openings **82** each having a width of at least 133 mm along the scanning direction.

Assuming that approximately 30 mm is appropriate for the distance (margin width **d7**; see FIG. 1) from each end of an opening **82** to a corresponding end of the shadow mask **81**, the

shadow mask **81** requires a length of  $133+30+30\approx 200$  mm for the width along the scanning direction.

The shadow mask **81** thus preferably has a short side length (that is, the width **d2**) of not less than 200 mm. The short side length is, however, not limited to not less than 200 mm if there is a change in the vapor deposition rate, the film thickness of a vapor-deposited film, and/or the allowable amount of the tact time.

The present embodiment assumes 30 mm/s for the rate of scanning the TFT substrate **10**.

FIG. **10** is a flowchart illustrating an example method for forming a predetermined pattern on the TFT substrate **10** with use of the vapor deposition device **50** of the present embodiment.

The following specifically describes, with reference to the flow illustrated in FIG. **10**, a method of FIG. **8** for forming luminescent layers **23R**, **23G**, and **23B** with use of the vapor deposition device **50**.

The method first, as illustrated in FIG. **3**, places (fixes) the shadow mask **81** above the vapor deposition source **85** in the vacuum chamber **60** with use of the mask holding member **87** via the mask tension mechanism **88**, and horizontally holds the shadow mask **81** under tension by the mask tension mechanism **88** so that no bending or elongation due to the self weight is caused to the shadow mask **81**. During this step, the method simultaneously (i) maintains the distance between the vapor deposition source **85** and the shadow mask **81** with use of the mask holding member **87** and (ii) carries out an alignment with use of the alignment markers **84** of the shadow mask **81** in such a manner that the substrate scanning direction is identical to the long-axis direction of the stripe-shaped openings **82** provided in the shadow mask **81**. The above step assembles the mask unit **80** (preparation of a mask unit).

The method next inserts the TFT substrate **10** in the vacuum chamber **60** and, as indicated in FIG. **10**, carries out a rough alignment with use of the alignment markers **221** of the TFT substrate **10** as the film formation substrate **200** so that each sub-pixel column of an identical color of the TFT substrate **10** has a direction that is identical to the substrate scanning direction (**S11**). The method holds the TFT substrate **10** with use of the substrate holding member **71** so that no bending due to the self weight is caused to the TFT substrate **10**.

The method then adjusts the gap **g1** (substrate-mask gap) between the TFT substrate **10** and the shadow mask **81** so that the gap is uniform, and places the TFT substrate **10** and the shadow mask **81** so that they face each other. This allows the TFT substrate **10** and the shadow mask **81** to be aligned with each other (**S13**). The present embodiment adjusted the gap **g1** between the TFT substrate **10** and the shadow mask **81** to approximately 200  $\mu\text{m}$  throughout the entire TFT substrate **10**.

The method next carried out vapor deposition of materials for the red luminescent layer **23R** with respect to the TFT substrate **10** while scanning the TFT substrate **10** at 30 mm/s.

The above step carried out a substrate scan in such a manner that the TFT substrate **10** passed through a position above the shadow mask **81**. The above step simultaneously carried out the scan and a precise alignment with use of the alignment markers **84** and **221** so that the openings **82** of the shadow mask **81** coincide with red sub-pixel **2R** columns (**S14**).

The luminescent layer **23R** was made of (i) 3-phenyl-4(1'-naphthyl)-5-phenyl-1,2,4-triazole (TAZ) (host material) and (ii) bis(2-(2'-benzo[4,5- $\alpha$ ]thienyl)pyridinato-N,C3')iridium (acetylacetonate) (btp2Ir(acac)) (red-light emitting dopant). These materials (red organic materials) were codeposited at

respective vapor deposition rates of 5.0 nm/s and 0.53 nm/s to form the luminescent layer 23R.

Vapor deposition particles of the red organic materials which particles are emitted from the vapor deposition source 85 are deposited, through the openings 82 of the shadow mask 81 and onto positions facing the respective openings 82 of the shadow mask 81, when the TFT substrate 10 passes through a position directly above the shadow mask 81. In the present embodiment, the TFT substrate 10 having passed through the position directly above the shadow mask 81 had the red organic materials deposited thereon at a film thickness of 25 nm.

This causes a vapor-deposited film having a striped shape to be formed on the TFT substrate 10 throughout a region from one end to the other end in a direction in which the TFT substrate 10 is moved (see FIG. 17).

The following describes, with reference to FIG. 11, a method for adjusting an alignment in S14 above.

FIG. 11 is a flowchart illustrating the alignment adjustment method. The alignment is adjusted as illustrated in the flow of FIG. 11.

The method first captures a substrate position of the TFT substrate 10 as the film formation substrate 200 with use of the image sensors 90 (S21).

Next, the image detecting section 101, on the basis of the image captured by the image sensors 90, detects respective images of (i) the alignment markers 221 of the TFT substrate 10 and of (ii) the alignment markers 221 of the shadow mask 81 (S22).

Then, the computing section 102 calculates, from the respective images of the alignment markers 221 and 84, the images having been detected by the image detecting section 101, the amount of positional difference between the alignment markers 221 and the alignment markers 84 to determine a correction value for a substrate position by computation (S23).

Next, the motor drive control section 103 drives the motor 72 on the basis of the correction value to correct the substrate position (S24).

Then, the image sensors 90 detect the substrate position as corrected, after which the steps S21 through S25 are repeated.

As described above, the present embodiment causes the image sensors 90 to repeatedly detect a substrate position to correct it. This makes it possible to simultaneously carry out a substrate scan and correct a substrate position, and consequently to form a film while carrying out a precise alignment between the TFT substrate 10 and the shadow mask 81.

The film thickness of the luminescent layer 23R can be adjusted on the basis of (i) a reciprocating scan (that is, reciprocating movement of the TFT substrate 10) and (ii) a scan rate. The present embodiment, after the scan in S14, (i) reversed the direction of scanning the TFT substrate 10, and (ii) further deposited the red organic materials by the same method as in S14 at the positions at which the red organic materials were deposited in S14. This formed a luminescent layer 23R having a film thickness of 50 nm.

The present embodiment, after the step S14, retrieved from the vacuum chamber 60 the TFT substrate 10 on which the luminescent layer 23R was formed (S15), and then formed a green luminescent layer 23G, with use of (i) a mask unit 80 for forming the green luminescent layer 23G and (ii) a vacuum chamber 60, in a manner similar to the above process of forming the luminescent layer 23R.

The present embodiment, after thus forming the luminescent layer 23G, formed a blue luminescent layer 23B, with use of (i) a mask unit 80 for forming the blue luminescent

layer 23B and (ii) a vacuum chamber 60, in a manner similar to the respective processes of forming the luminescent layers 23R and 23G.

Specifically, the present embodiment, for each of the processes of forming the luminescent layers 23G and 23B, prepared a shadow mask 81 having openings 82 at positions for a corresponding one of the luminescent layers 23G and 23B. The present embodiment placed each shadow mask 81 in a vacuum chamber 60 for forming a corresponding one of the luminescent layers 23G and 23B, and thus scanned the TFT substrate 10 for vapor deposition while carrying out an alignment so that the openings 82 of the shadow mask 81 coincide with a corresponding one of (i) sub-pixel 2G columns and (ii) sub-pixel 2B columns.

The luminescent layer 23G was made of (TAZ) (host material) and Ir(ppy) 3 (green-light emitting dopant). These materials (green organic materials) were codeposited at respective vapor deposition rates of 5.0 nm/s and 0.67 nm/s to form the luminescent layer 23G.

The luminescent layer 23B was made of TAZ (host material) and 2-(4'-t-butyl phenyl)-5-(4"-biphenyl)-1,3,4-oxadiazole (t-Bu PBD) (blue-light emitting dopant). These materials (blue organic materials) were codeposited at respective vapor deposition rates of 5.0 nm/s and 0.67 nm/s to form the luminescent layer 23B.

The luminescent layers 23G and 23B each had a film thickness of 50 nm.

The above steps prepared a TFT substrate 10 on which were formed respective patterns of the luminescent layers 23R, 23G, and 23B having respective colors of red (R), green (G), and blue (B).

By the way, in a case where vapor deposition layers (in the present embodiment, the luminescent layers 23R, 23G, and 23B of the organic EL elements 20) are formed by relative movement between the shadow mask 81 and the TFT substrate 10, the following problems can arise. FIG. 13 is a view schematically illustrating how the TFT substrate 10 is configured before formation of the luminescent layers 23R, 23G, and 23B.

As illustrated in FIG. 7, the TFT substrate 10 has the plurality of pixels that are arranged two-dimensionally (in the present embodiment, arranged in a matrix). In the following description, a region in which the plurality of pixels are arranged will be referred to as a pixel region  $A_G$ .

As mentioned above, the wires 14 run in a mesh-like manner in directions in which the plurality of pixels in the pixel region  $A_G$  are aligned, and the wires 14 are drawn out of the pixel region  $A_G$  so as to be electrically connected to an external circuit. The external circuit is, for example, a flexible film cable FC or an IC (Integrated circuit).

Terminals of the wires 14 that are drawn out of the pixel region  $A_G$  are gathered in a plurality of regions outside the pixel region  $A_G$  (see FIG. 13). Such regions in which the terminals of the wires 14 are gathered will be hereinafter referred to as terminal section regions.

Specifically, a plurality of terminal section regions A1 through A4 are provided at an outer side of and adjacently to respective sides L1 through L4 (at an outer side of and along the respective sides L1 through L4) of a rectangle which the matrix forms so as to surround the pixel region  $A_G$ .

It is assumed here that (i) a terminal section region located on the left hand of the pixel region  $A_G$  is the terminal section region A1, (ii) a terminal section region located on the right hand of the pixel region  $A_G$  is the terminal section region A2, (iii) a terminal section region located on the upper hand of the pixel region  $A_G$  is the terminal section region A3, and (iv) a

terminal section region located on the lower hand of the pixel region  $A_G$  is the terminal section region  $A_4$ , as illustrated in FIG. 13.

Each of the terminals of the wires **14** (except for terminals connected to the second electrode **26**) is located in a terminal section region adjacent to a side closest to the terminal out of the four sides  $L_1$  through  $L_4$  of the rectangle.

Assuming that the TFT substrate **10** is moved in the left-right direction of FIG. 13, the terminal section regions  $A_1$  and  $A_2$ , which are close to the sides  $L_1$  and  $L_2$  that are vertical to the direction in which the TFT substrate **10** is moved, are referred to as vertical-side terminal section regions  $A_1$  and  $A_2$ , whereas the terminal section regions  $A_3$  and  $A_4$ , which are close to the sides that are parallel to the direction in which the TFT substrate **10** is moved, are referred to as parallel-side terminal section regions  $A_3$  and  $A_4$ .

Meanwhile, connection sections to be connected to the second electrode **26** are provided in regions different from the terminal section regions  $A_1$  through  $A_4$ . In the present embodiment, such connection sections to be connected to the second electrode **26** are provided at an outer side of and adjacently to the respective upper and lower sides of the rectangle. Regions where such connection sections to be connected to the second electrode **26** are provided will be hereinafter referred to as second electrode connection sections. As illustrated in FIG. 13, an upper second electrode connection section will be hereinafter referred to as a second electrode connection section  $A_5$ , whereas a lower second electrode connection section will be hereinafter referred to as a second electrode connection section  $A_6$ .

In FIG. 13, the pixel region  $A_G$  and the second electrode connection sections  $A_5$  and  $A_6$  are sealed by the sealing substrate **40**, whereas the terminal section regions  $A_1$  through  $A_4$  are exposed to the outside without being sealed.

FIG. 14 is a view illustrating a state where the TFT substrate **10** sealed by the sealing substrate **40** is about to be connected to the flexible film cable FC which is one example of the external circuit. FIG. 15 is a view illustrating a configuration around the terminals of the wires **14** located in the vertical-side terminal section region  $A_1$ .

Each of the terminals of the wires **14** whose terminals are gathered in the vertical-side terminal section region  $A_1$  is connected, in a connection region **202**, to a connection terminal  $FC_T$  of the flexible film cable FC via an anisotropically-conductive adhesive film (ACF) or the like, for example, as illustrated in FIG. 15. The same is true for the terminals of the wires **14** whose terminals are gathered in the vertical-side terminal section region  $A_2$  and for the terminals of the wires **14** whose terminals are gathered in the parallel-side terminal section regions  $A_3$  and  $A_4$ .

It is assumed here that, through relative movement between the shadow mask **81** and the TFT substrate **10**, an organic film (e.g., the luminescent layer **23R**) is vapor-deposited on the TFT substrate **10**, which has the vertical-side terminal section regions  $A_1$  through  $A_4$  exposed to an outside, throughout a region from one end to the other end in a direction of the movement.

A vapor deposition region can be caused to substantially coincide with the pixel region  $A_G$  by appropriately setting a range of the openings **82** in a direction vertical to the direction of the movement. This makes it possible to prevent the organic film from being vapor-deposited on the parallel-side terminal section regions  $A_3$  and  $A_4$ .

Meanwhile, the organic film is vapor-deposited on the vertical-side terminal section regions  $A_1$  and  $A_2$ , so that the connection regions **202** of the terminals located in the verti-

cal-side terminal section regions  $A_1$  and  $A_2$  are covered with the organic film as illustrated in FIG. 15.

In a case where the organic film has high electrical resistance, there arises a problem that good electrical connection between (i) the wires **14** having respective terminals in the vertical-side terminal section regions  $A_1$  and  $A_2$  and (ii) the connection terminal  $FC_T$  of the flexible film cable FC cannot be established. Failure to establish good electrical connection with the connection terminal  $FC_T$  of the flexible film cable FC results in that the flexible film cable FC peels off from the TFT substrate **10** or in that the organic EL display device **1** has a display failure.

Meanwhile, in a case where the organic film has low electrical resistance, there arises a problem that an electrical leakage occurs via the organic film.

It is therefore necessary to take measures for preventing the organic film from being vapor-deposited and formed on the terminals located in the vertical-side terminal section regions  $A_1$  and  $A_2$ . Such regions where the organic film should not be vapor-deposited will be hereinafter referred to as vapor deposition unnecessary regions.

One of the measures is to prevent vapor deposition on the vapor deposition unnecessary regions by blocking vapor deposition of the organic film with the use of a shutter **89**, specifically, to close the shutter **89** when the vapor deposition unnecessary regions reach the openings **82** of the shadow mask **81**.

However, this causes a difference among parts of the TFT substrate **10** in terms of period of time for which the parts face the openings **82** since each of the openings **82** has a length in the direction of the movement. This may leave a region, above the openings **82** of the shadow mask **81**, in which the organic film should be vapor-deposited but has not been vapor-deposited when the shutter **89** is closed. Closing the shutter in such a state causes shortage of a vapor deposition amount in the region in which the organic film should be vapor-deposited. This leads to a problem that an appropriate thickness of the vapor-deposited film cannot be secured in the region.

Another one of the measures is to wipe away the organic film with the use of an organic solvent in a later step. However, this causes problems such as occurrence of a residue of the organic solvent and introduction of dust.

In view of the above problems, the TFT substrate **10** of the present embodiment is arranged such that the terminals (except the terminals connected to the second electrode **26**) of the wires **14** are gathered not to be located in regions (hereinafter referred to as "vapor deposition regions") on which the vapor-deposited film is to be vapor-deposited.

FIG. 16 is a view illustrating how the plurality of wires **14** are disposed on the TFT substrate **10**. FIG. 17 is a view illustrating a state where a plurality of TFT substrates **10** of the present embodiment are arranged in a matrix and vapor deposition is simultaneously carried out on the plurality of TFT substrates **10**.

Specifically, as illustrated in FIGS. 16 and 17, the terminals of the wires **14**, which have been gathered in the vertical-side terminal section regions  $A_1$  and  $A_2$  in the conventional technique, are gathered in the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$  each of which is provided at an outer side of and adjacently to a side extending in parallel with a moving direction in which the TFT substrate **10** is moved relative to the shadow mask **81**. In other words, as illustrated in FIG. 16, the wires **14** are designed so that terminals of some wires **14**, which are other than the wires **14** connected to the second electrode **26**, are gathered in the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$ .

According to the wiring arrangement illustrated in FIG. 16, terminals of wires 14, which extend in a left-right direction, are gathered in the parallel-side terminal section region  $P_{T2}$  located on the lower side, and terminals of wires 14, which extend in an up-and-down direction, are gathered in the parallel-side terminal section region  $P_{T1}$  located on the upper side.

Note that the present embodiment employs an arrangement in which (i) second electrode connection section  $P_{T3}$  is provided between the parallel-side terminal section region  $P_{T1}$  and the side of the rectangle in the vicinity of the parallel-side terminal section region  $P_{T1}$  and (ii) the second electrode connection section  $P_{T4}$  is provided between the parallel-side terminal section region  $P_{T2}$  and the side of the rectangle in the vicinity of the parallel-side terminal section region  $P_{T2}$ . Note, however, that the second electrode connection sections  $P_{T3}$  and  $P_{T4}$  are not limited to these locations.

With the arrangement, it is possible to prevent the organic film from being vapor-deposited on the terminals of the wires 14 gathered in the vertical-side terminal section regions A1 and A2. As a result, electrical connection can be well established between the terminals of the gate lines 14G and the connection terminal  $FC_T$  of the flexible film cable FC.

Further, the arrangement eliminates the need for the conventional measure of wiping away the organic film formed in the vertical-side terminal section regions A1 and A2 with the use of an organic solvent in a later step. This allows a reduction in time and cost for production.

Moreover, it is possible to prevent the problems, which conventionally occur due to wiping of the vapor-deposited film with the use of an organic solvent, such as (i) occurrence of a residue due to insufficient wiping and (ii) occurrence of a foreign substance which causes connection failure with an external circuit and ultimately causes a reduction in yield of an organic EL display device. In addition, it is possible to prevent the organic solvent from damaging the sealing substrate 40 and the like, thereby preventing a reduction in reliability of the organic EL display device 1.

Moreover, there is no need for addition of any step and device since it is only necessary to change design of the wires on the TFT substrate 10.

#### Second Embodiment

The following description will discuss a film formation substrate in accordance with a second embodiment of the present invention. Note that the present embodiment mainly describes differences from the first embodiment. The same reference numerals are given to constituent members which have functions identical with those of the constituent members employed in the first embodiment, and explanations of such constituent members are omitted. FIG. 18 is a view schematically illustrating a configuration of a TFT substrate (film formation substrate) in accordance with the second embodiment.

A TFT substrate of the present embodiment is different from that of the first embodiment in locations in which second electrode connection sections  $P_{T3}$  and  $P_{T4}$  are provided.

Specifically, in the first embodiment, (i) the second electrode connection section  $P_{T3}$  is provided between a side, which is in parallel with a move direction in which the TFT substrate 10 is moved relative to the shadow mask 81, and the parallel-side terminal section region  $P_{T1}$ , and (ii) the second electrode connection section  $P_{T4}$  is provided between another side, which is in parallel with the moving direction, and the parallel-side terminal section region  $P_{T2}$ . On the other hand, in the present embodiment, second electrode connection sec-

tions  $P_{T3}'$  and  $P_{T4}'$  are arranged in respective regions each of which is located at an outer side of and adjacently to a corresponding side intersecting with the move direction (see FIG. 18).

In this case, the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  are to be covered with an organic film. However, the organic film is a stripe-shaped pattern film, and therefore no organic film exists between the stripes. With the configuration, it is possible to connect wires 14 directly to a second electrode 26 by causing a terminal of each of the wires 14, which terminal is to be connected to the second electrode 26, to be exposed through a corresponding region between the stripes of the organic film.

Here, unlike the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$ , the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  do not require accuracy in locations in which the wires are connected with the second electrode. Moreover, the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  can have a larger contact area by enlarging a connection region 202 in which the wires 14 are connected with the second electrode. That is, the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  have design freedom higher than that of the terminal section regions  $P_{T1}$  and  $P_{T2}$ . Therefore, the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  hardly cause defective electrical connection even in a case where electrical connections are provided between stripes of the stripe-shaped organic film.

Even in a case where the organic film is an electrically conductive film, electrical leakage would not be caused because each of the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  is a single terminal (i.e., a single element), unlike the case where terminals, which are connected to the organic film for corresponding wires, are gathered in the terminal section regions  $P_{T1}$  and  $P_{T2}$ .

As such, the present embodiment can bring about an effect similar to that of the first embodiment. In addition to this, it is possible to shorten a length of the organic EL display device 1 in a direction intersecting with the moving direction, in which the TFT substrate 10 is moved relative to the shadow mask 81, by forming only the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$  along the sides extending in parallel with the moving direction.

The present invention is not limited to the embodiments, but can be altered by a skilled person in the art within the scope of the claims. An embodiment derived from a proper combination of technical means disclosed in respective different embodiments is also encompassed in the technical scope of the present invention.

For example, in order to differentiate total thicknesses of organic films for respective colors, it is possible to selectively provide organic layers (e.g., hole transfer layers), other than the luminescent layer, for respective pixels by carrying out a vapor deposition formation with the use of the shadow mask, as with the foregoing method. In this case, the film formation substrate of the present invention is exemplified by a TFT substrate 10 which is in a state immediately before a hole transfer layer is formed on the TFT substrate 10.

The vapor deposition device 50 may include, instead of the substrate moving mechanism 70, (i) a substrate holding member 71 (for example, an electrostatic chuck) for fixing the film formation substrate 200 and (ii) a mask unit moving mechanism for moving the mask unit 80 relative to the film formation substrate 200 while maintaining the respective positions of the shadow mask 81 and the vapor deposition source 85 relative to each other. The vapor deposition device may alternatively include both the substrate moving mechanism 70 and a mask unit moving mechanism.

In other words, the film formation substrate **200** and the mask unit **80** simply need to be so provided that at least one of them is moveable relative to the other. The advantages of the present invention can be achieved regardless of which of the film formation substrate **200** and the mask unit **80** is arranged to move.

In the case where the film formation substrate **200** is moved relative to the mask unit **80** as described above, the shadow mask **81** and the vapor deposition source **85** simply need to be fixed in position relative to each other, but do not necessarily need to be integrated with each other.

The mask unit **80** may be arranged, for example, such that (i) the vapor deposition source **85** is fixed to, for example, a bottom wall among inner walls of the vacuum chamber **60**, (ii) the mask holding member **87** is fixed to one of the inner walls of the vacuum chamber **60**, and consequently (iii) the shadow mask **81** and the vapor deposition source **85** are fixed in position relative to each other.

The present embodiment describes an example case in which the openings **82** of the shadow mask **81** are aligned with the injection holes **86** of the vapor deposition source **85** so that the injection holes **86** are each positioned inside one of the openings **82** in a plan view and that the openings **82** are provided in a one-to-one correspondence with the injection holes **86**. The present embodiment is, however, not limited to such an arrangement. The openings **82** do not necessarily need to be provided (i) to face the injection holes **86** or (ii) in a one-to-one correspondence with the injection holes **86**.

The present embodiment describes an example case in which both the openings **82** of the shadow mask **81** and the injection holes **86** of the vapor deposition source **85** are arranged one-dimensionally. The present embodiment is, however, not limited to such an arrangement. The openings **82** of the shadow mask **81** and the injection holes **86** of the vapor deposition source **85** simply need to be provided to face each other, and may thus be arranged two-dimensionally.

The present embodiment describes an example case involving a plurality of openings **82** in the shadow mask **81** and a plurality of injection holes **86** in the vapor deposition source **85**. The present embodiment is, however, not limited to such an arrangement. The shadow mask **81** simply needs to include at least one opening **82**, whereas the vapor deposition source **85** simply needs to include at least one injection hole **86**.

In other words, the present embodiment may alternatively be arranged such that the shadow mask **81** includes only one opening **82** and that the vapor deposition source **85** includes only one injection hole **86**. Even this arrangement makes it possible to form a predetermined pattern on the film formation substrate **200** by (i) moving at least one of the mask unit **80** and the film formation substrate **200** relative to the other and (ii) sequentially depositing vapor deposition particles onto the vapor deposition region **210** of the film formation substrate **200** through the opening **82** of the shadow mask **81**.

The present embodiment describes an example case in which the shadow mask **81** includes slit-shaped openings **82**. The shape of the openings **82** can, however, be simply set as appropriate to form a desired vapor deposition pattern, and is thus not particularly limited to any specific one.

The present embodiment describes an example method for producing, as described above, an organic EL display device **1** of the bottom emission type, which extracts light from the TFT substrate **10** side. The present embodiment is, however, not limited to such production. The present invention is also suitably applicable to an organic EL display device **1** of a top emission type, which extracts light from the sealing substrate **40** side.

The present embodiment describes an example case that uses a glass substrate as a supporting substrate for each of the TFT substrate **10** and the sealing substrate **40**. The present embodiment is, however, not limited to such an arrangement.

The respective supporting substrates for the TFT substrate **10** and the sealing substrate **40** may, for example, each be, other than a glass substrate, a transparent substrate such as a plastic substrate in the case where the organic EL display device **1** is an organic EL display device of the bottom emission type. In the case where the organic EL display device **1** is an organic EL display device of the top emission type, the respective supporting substrates may, for example, each be an opaque substrate such as a ceramics substrate other than the above transparent substrate.

The present embodiment describes an example case involving an anode (in the present embodiment, the first electrode **21**) formed in a matrix. The anode is, however, not particularly limited in terms of shape, material, or size as long as it has the function as an electrode for supplying positive holes to an organic EL layer. The anode may have, for example, a stripe shape. By the nature of an organic EL element, at least one of the anode and the cathode is preferably transparent. An organic EL element typically includes a transparent anode.

The present embodiment describes an example method for producing an active matrix organic EL display device which has a TFT in each pixel. The present embodiment is, however, not limited to such production. The present invention is also suitably applicable to a passive matrix organic EL display device **1** which has no TFT in each pixel.

In the present embodiment, the scan rate, the vapor deposition rate, and the like can be set as appropriate.

The gap **g1** between the TFT substrate **10** serving as the film formation substrate **200** and the shadow mask **81** and the gap **g2** between the vapor deposition source **85** and the shadow mask **81** can be set as appropriate.

The gap **g1** between the TFT substrate **10** and the shadow mask **81** may be adjusted as appropriate as long as (i) the gap is fixed and (ii) the TFT substrate **10** and the shadow mask **81** do not come into contact with each other. The gap **g2** may be adjusted as appropriate in consideration of (i) distribution of, for example, spatial spread of vapor deposition particles and (ii) influence of heat radiated from the vapor deposition source **85**.

A region in which the terminals of the wires **14** are gathered is not limited to the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$ . For example, as indicated by a region **x** in FIG. **17**, a region in which the terminals of the wires **14** are gathered can be provided on a diagonal line of the rectangle, which is formed by the matrix, so that the region is adjacent to the rectangle. That is, the region in which the terminals of the wires **14** are gathered is not limited in particular, provided that the region is outside the vapor deposition region **210**.

In the above embodiments, the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$  are provided. Note, however, that the terminals of the wires **14** may be gathered in any one of the parallel-side terminal section regions  $P_{T1}$  and  $P_{T2}$ . According to the first embodiment, the second electrode connection sections  $P_{T3}$  and  $P_{T4}$  are provided, and, according to the second embodiment, the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$  are provided. Note, however, that the terminals of the wires **14** may be gathered in any one of the second electrode connection sections  $P_{T3}$  and  $P_{T4}$  or in any one of the second electrode connection sections  $P_{T3}'$  and  $P_{T4}'$ .

The present invention is applicable not only to production of the organic EL display device **1**, but also to production of other devices which face a problem of formation of a vapor-

deposited film on a terminal section region in a case where vapor deposition is carried out by relative movement of a substrate and a shadow mask.

[Overview]

As above described, according to the film formation substrate of an embodiment of the present invention, the pixel region is a rectangular region in which the plurality of pixels are arranged in a matrix; at least one of four sides of a rectangle formed by the pixel region extends in parallel with the moving direction; and the terminals of the plurality of wires are gathered (i) in a region outside the vapor deposition layer formation region and (ii) at an outer side of the at least one of four sides so as to be arranged along the at least one of four sides.

According to the configuration, the terminals of the plurality of wires are gathered (i) in the region outside the vapor deposition layer formation region and (ii) at an outer side of the at least one of four sides so as to be arranged along the at least one of four sides. This makes it possible to shorten a length of the plurality of wires as much as possible, as compared with a case where the location in which the terminals are gathered is set to another location.

According to the film formation substrate of an embodiment of the present invention, a connection section of a second electrode for injecting electrons into a luminescent layer, which is formed on the film formation substrate, is provided (i) in a region outside the vapor deposition layer formation region and (ii) at an outer side of the at least one of four sides so as to extend along the at least one of four sides.

According to the film formation substrate of an embodiment of the present invention, a connection section of a second electrode for injecting electrons into a luminescent layer, which is formed on the film formation substrate, is provided in the vapor deposition layer formation region.

According to the configuration, the connection section of the second electrode is gathered in the vapor deposition layer formation region. This allows terminals, which are of wires other than those connected with the second electrode, to be gathered in a space in which, conventionally, connection sections of wires to be connected to the second electrode have been provided.

Note that, in this case, the connection section of the second electrode is not directly connected to an external circuit but is connected to the external circuit via the terminals that are formed outside the vapor deposition layer formation region.

According to the film formation substrate of an embodiment of the present invention, the pixel region is a rectangular region in which the plurality of pixels are arranged in a matrix; at least one of four sides of a rectangle formed by the pixel region extends in parallel with the moving direction; and the connection section of the second electrode is provided (i) at an outer side of another side of the rectangle, which another side extends in a direction that intersects with the at least one of four sides extending in parallel with the moving direction, and (ii) so as to extend along the another side.

According to the embodiment of the present invention, the connection section of the second electrode is provided (i) at an outer side of another side of the rectangle, which another side extends in a direction that intersects with the at least one of four sides extending in parallel with the moving direction, and (ii) so as to extend along the another side. This makes it possible to shorten a length of wires, which are connected to the connection section of the second electrode, as much as possible.

The organic EL display device of an embodiment of the present invention includes: the film formation substrate which has any of the above described configurations and on

which the vapor deposition layer has been vapor-deposited, the vapor deposition layer including an organic EL layer made of an organic EL element that emits light in response to an applied electric current.

According to the configuration, it is possible to provide the organic EL display device that can achieve the effect of any of the foregoing configurations of the present invention.

## INDUSTRIAL APPLICABILITY

The film formation substrate of the present invention is suitably applicable to, for example, a device and method for producing an organic EL display device which are used in a process of, for example, selective application formation of an organic layer for an organic EL display device.

## REFERENCE SIGNS LIST

- 1: Organic EL display device
- 2: Pixel
- 10: TFT substrate (film formation substrate)
- 26: Second electrode
- 50: Vapor deposition device
- 81: Shadow mask (vapor deposition mask)
- 82: Opening
- 85: Vapor deposition source
- 86: Injection hole
- 200: Film formation substrate
- 210: Vapor deposition region
- 211: Vapor-deposited film (vapor deposition layer)
- 14: Wire
- A<sub>G</sub>: Pixel region

The invention claimed is:

1. A film formation substrate on which vapor deposition layers are formed by use of a vapor deposition device which includes (i) a vapor deposition source having an injection hole from which vapor deposition particles are injected and (ii) a vapor deposition mask facing the vapor deposition source and having an opening through which the vapor deposition particles injected from the injection hole are deposited so as to form the vapor deposition layers,

said film formation substrate comprising:

a plurality of pixels two-dimensionally arranged in a pixel region; and

a plurality of wires electrically connected to the respective plurality of pixels, the plurality of wires running in a mesh-like manner in directions in which the plurality of pixels in the pixel region are aligned and being drawn out of the pixel region, each of the plurality of pixels including a plurality of sub-pixels,

the vapor deposition layers being formed in a vapor deposition layer formation region, by injecting the vapor deposition particles from the injection hole while moving said film formation substrate relative to the vapor deposition mask in a moving direction so that the pixel region passes a region facing the opening, the vapor deposition layer formation region including the pixel region,

the film formation substrate including, in this order, (i) the plurality of wires, (ii) a first electrode having a two-dimensional pattern corresponding to each of the sub-pixels, (iii) the vapor deposition layers including a luminescent layer, and (iv) a second electrode formed unintermittently over the sub-pixels having different colors and located adjacent to one another, one of the first electrode and the second electrode being for injecting electrons to the luminescent layer,

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first terminals of the plurality of wires other than wires connected with the second electrode being disposed outside the vapor deposition layer formation region, and second terminals of the plurality of wires connected with the second electrode being disposed inside the vapor deposition layer formation region.

2. The film formation substrate as set forth in claim 1, wherein:

the pixel region is a rectangular region in which the plurality of pixels are arranged in a matrix;

at least one of four sides of a rectangle formed by the pixel region extends in parallel with the moving direction; and the first terminals are disposed at an outer side of the at least one of four sides so as to be arranged along the at least one of four sides.

3. The film formation substrate as set forth in claim 1, wherein:

the pixel region is a rectangular region in which the plurality of pixels are arranged in a matrix;

at least one of four sides of a rectangle formed by the pixel region extends in parallel with the moving direction; and the second terminals are provided (i) at an outer side of another side of the rectangle, which another side extends in a direction that intersects with the at least one of four sides extending in parallel with the moving direction, and (ii) so as to extend along the another side.

4. An organic EL display device comprising:

a film formation substrate recited in claim 1 on which the vapor deposition layers have been vapor-deposited,

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the vapor deposition layers including an organic EL layer made of an organic EL element that emits light in response to an applied electric current.

5. The film formation substrate as set forth in claim 1, wherein the second terminals are sealed in a sealing region.

6. The film formation substrate as set forth in claim 1, wherein the first terminals are provided outside a sealing region.

7. The film formation substrate as set forth in claim 1, wherein the plurality of wires include a plurality of gate lines and a plurality of source lines.

8. The film formation substrate as set forth in claim 1, wherein the second terminals are exposed between the vapor deposition layers formed in a striped shape.

9. The film formation substrate as set forth in claim 1, wherein the second terminals are provided outside the pixel region.

10. The film formation substrate as set forth in claim 1, wherein the vapor deposition layers are formed in a striped shape throughout the region from one end to the other end of said film formation substrate in the moving direction in which said film formation substrate is moved relative to the vapor deposition mask.

11. The film formation substrate as set forth in claim 10, wherein the second terminals are provided (i) between the vapor deposition layers formed in the striped shape and (ii) outside the pixel region.

12. The film formation substrate as set forth in claim 1, wherein the first terminals are disposed outside the pixel region.

\* \* \* \* \*

|                |                                                                                  |         |            |
|----------------|----------------------------------------------------------------------------------|---------|------------|
| 专利名称(译)        | 形成薄膜的基板和有机EL显示装置                                                                 |         |            |
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| 其他公开文献         | US20130285038A1                                                                  |         |            |
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# 摘要(译)

在TFT基板(10)上，通过使用包括(i)气相沉积源(50)形成气相沉积层。具有注入孔(86)和(ii)具有开口(82)的气相沉积掩模(81)通过其沉积从注入孔(86)注入的气相沉积颗粒以形成气相沉积层。TFT基板(10)具有在像素区域(AG)中二维排列的多个像素，以及多个导线的端子(14)，其与多个像素电连接，聚集在气相沉积层形成区域的外部。

